

带有双集成比较器的 **INA30x 36V** 过流保护 高速精密电流传感放大器

1 特性

- 宽共模输入范围: $-0.1V$ 至 $36V$
- 双比较器输出:
 - INA302: 两个独立的超限警报
 - INA303: 窗口比较器
 - 阈值水平单独设置
 - 比较器 1 警报响应: $1\mu s$
 - 比较器 2 可调延迟: $2\mu s$ 至 $10s$
 - 具有独立锁存控制模式的开漏极输出
- 高精度放大器:
 - 偏移电压: $30\mu V$ (最大值, A3 版本)
 - 偏移电压漂移: $0.5\mu V/\text{°C}$ (最大值)
 - 增益误差: 0.15% (最大值, A3 版本)
 - 增益误差漂移: $10\text{ppm}/\text{°C}$
- 可用放大器增益:
 - INA302A1、INA303A1: $20V/V$
 - INA302A2、INA303A2: $50V/V$
 - INA302A3、INA303A3: $100V/V$

2 应用范围

- 过流保护
- 电机控制
- 电源保护
- 计算机和服务器
- 电信设备

3 说明

INA302 和 INA303 器件具有一个高共模、双向电流传感放大器和两个高速比较器，用于检测超出范围的电流状况。INA302 比较器配置为检测和响应过流状况。

INA303 比较器配置为在窗口配置中响应过流和欠流状况。该器件每个一个可调节限制阈值范围，该范围通过一个外部限值设定电阻进行设置。这些电流分流监控器可在独立于电源的 $-0.1V$ 至 $36V$ 共模电压范围内测量差动电压信号。

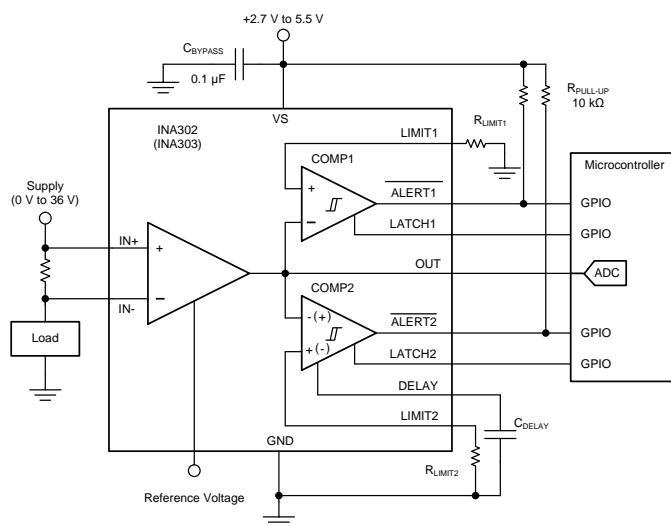
开漏极警报输出可配置为在透明模式（输出状态与输入状态保持一致）或锁存模式（警报输出在锁存复位时清除）下运行。比较器 1 的警报响应时间小于 $1\mu s$ ，而比较器 2 的警报响应时间通过外部电容器进行设置，范围介于 $2\mu s$ 至 $10s$ 之间。

此器件由 $2.7V$ 至 $5.5V$ 的单个电源供电，消耗的最大电源电流为 $950\mu A$ 。该器件具有扩展级工作温度范围（ -40°C 至 $+125\text{°C}$ ），并且采用 14 引脚 TSSOP 封装。

器件信息

器件编号	封装	封装尺寸
INA302	TSSOP (14)	$4.40\text{mm} \times 5.00\text{mm}$
INA303	TSSOP (14)	$4.40\text{mm} \times 5.00\text{mm}$

典型应用



Copyright © 2017, Texas Instruments Incorporated



An **IMPORTANT NOTICE** at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. **PRODUCTION DATA**.

English Data Sheet: **SBOS775**

目录

1	特性	1	8	Application and Implementation	28
2	应用范围	1	8.1	Application Information	28
3	说明	1	8.2	Typical Application	28
4	修订历史记录	2	9	Power Supply Recommendations	30
5	Pin Configuration and Functions	3	10	Layout	30
6	Specifications	4	10.1	Layout Guidelines	30
6.1	Absolute Maximum Ratings	4	10.2	Layout Example	31
6.2	ESD Ratings	4	11	器件和文档支持	32
6.3	Recommended Operating Conditions	4	11.1	文档支持	32
6.4	Thermal Information	4	11.2	相关链接	32
6.5	Electrical Characteristics	5	11.3	接收文档更新通知	32
6.6	Typical Characteristics	7	11.4	社区资源	32
7	Detailed Description	14	11.5	商标	32
7.1	Overview	14	11.6	静电放电警告	32
7.2	Functional Block Diagram	14	11.7	Glossary	32
7.3	Feature Description	15	12	机械、封装和可订购信息	32
7.4	Device Functional Modes	23			

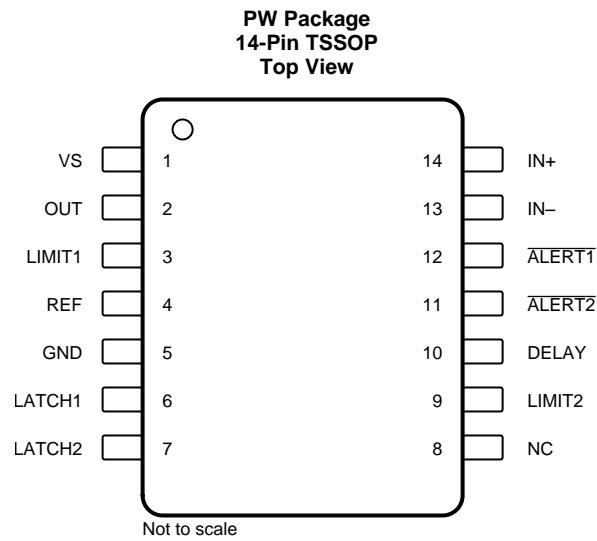
4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision A (February 2017) to Revision B	Page
已更改 y-axis units from 0.5 V/div to 1 V/div and changed (INA30xA1) to (INA30x) in title of <i>Comparator 1 Total Propagation Delay</i> figure	12
已更改 y-axis units from 0.5 V/div to 1 V/div and changed (INA303A1) to (INA303) in title of <i>Comparator 2 Total Propagation Delay</i> figure	12
已删除 <i>Comparator 1 Total Propagation Delay</i> (INA30xA2), <i>Comparator 1 Total Propagation Delay</i> (INA30xA3), <i>Comparator 2 Total Propagation Delay</i> (INA303A2), and <i>Comparator 2 Total Propagation Delay</i> (INA303A3) figures	12
已更改 (INA303A1) to (INA303) in title of <i>Comparator 2 Total Propagation Delay</i> figure	12
已删除 <i>Comparator 2 Total Propagation Delay</i> (INA303A2) and <i>Comparator 2 Total Propagation Delay</i> (INA303A3) figures	12
已添加 <i>Comparator 2 Total Propagation Delay</i> (INA302A1) and <i>Comparator 2 Total Propagation Delay</i> (INA302A1) figures	12

Changes from Original (September 2016) to Revision A	Page
投入生产	1

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	VS	Analog	Power supply, 2.7 V to 5.5 V
2	OUT	Analog output	Output voltage
3	LIMIT1	Analog input	ALERT1 threshold limit input; see the Setting Alert Thresholds section for details on setting the limit threshold
4	REF	Analog input	Reference voltage, 0 V to VS
5	GND	Analog	Ground
6	LATCH1	Digital input	Transparent or latch mode selection input
7	LATCH2	Digital input	Transparent or latch mode selection input
8	NC	—	No internal connection
9	LIMIT2	Analog input	ALERT2 threshold limit input; see the Setting Alert Thresholds section for details on setting the limit threshold
10	DELAY	Analog input	Delay timing input; see the Alert Outputs section for details on setting the delayed alert response for comparator 2
11	ALERT2	Analog output	Open-drain output; active-low. This pin is an overlimit alert for the INA302 and an underlimit alert for the INA303.
12	ALERT1	Analog output	Open-drain output, active-low overlimit alert
13	IN-	Analog input	Connect to load side of the current-sensing resistor
14	IN+	Analog input	Connect to supply side of the current-sensing resistor

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Supply voltage, V_S		6		V
Analog inputs (IN+, IN-)	Differential (V_{IN+}) – (V_{IN-}) ⁽²⁾	–40	40	V
	Common-mode ⁽³⁾	GND – 0.3	40	
Analog input	LIMIT1, LIMIT2, DELAY, V_{REF}	GND – 0.3	(V_S) + 0.3	V
Analog output	OUT	GND – 0.3	(V_S) + 0.3	V
Digital input	LATCH1, LATCH2	GND – 0.3	(V_S) + 0.3	V
Digital output	ALERT1, ALERT2	GND – 0.3	6	V
Junction temperature, T_J			150	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) V_{IN+} and V_{IN-} are the voltages at the IN+ and IN– pins, respectively.

(3) Input voltage can exceed the voltage shown without causing damage to the device if the current at that pin is limited to 5 mA.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±3000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CM}	Common-mode input voltage		12		V
V_S	Operating supply voltage		5		V
T_A	Operating free-air temperature	–40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		INA30x	UNIT
		PW (TSSOP)	
		14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	110.2	°C/W
$R_{\theta JC(\text{top})}$	Junction-to-case (top) thermal resistance	35.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	53.2	°C/W
ψ_{JT}	Junction-to-top characterization parameter	2.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	52.4	°C/W
$R_{\theta JC(\text{bot})}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

at $T_A = 25^\circ\text{C}$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_{\text{REF}} = V_S / 2$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, $V_{\text{LIMIT1}} = 3 \text{ V}$, and $V_{\text{LIMIT2}} = 3 \text{ V}$ (INA302) or $V_{\text{LIMIT2}} = 2 \text{ V}$ (INA303) (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
INPUT							
V_{CM}	Common-mode input voltage range		-0.1	36	36	V	
V_{IN}	Differential input voltage range	$V_{\text{IN}} = V_{\text{IN+}} - V_{\text{IN-}}$, $V_{\text{REF}} = V_S / 2$, A1 versions	0		± 125	mV	
		$V_{\text{IN}} = V_{\text{IN+}} - V_{\text{IN-}}$, $V_{\text{REF}} = V_S / 2$, A2 versions	0		± 50		
		$V_{\text{IN}} = V_{\text{IN+}} - V_{\text{IN-}}$, $V_{\text{REF}} = V_S / 2$, A3 versions	0		± 25		
CMRR	Common-mode rejection ratio	$V_{\text{IN+}} = 0 \text{ V}$ to 36 V , $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, A1 versions	100	114		dB	
		$V_{\text{IN+}} = 0 \text{ V}$ to 36 V , $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, A2 versions	106	118			
		$V_{\text{IN+}} = 0 \text{ V}$ to 36 V , $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, A3 versions	110	120			
V_{OS}	Offset voltage, RTI ⁽¹⁾	A1 versions		± 15	± 80	μV	
		A2 versions		± 10	± 50		
		A3 versions		± 5	± 30		
dV_{OS}/dT	Offset voltage drift, RTI ⁽¹⁾	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		0.02	0.25	$\mu\text{V}/^\circ\text{C}$	
PSRR	Power-supply rejection ratio	$V_S = 2.7 \text{ V}$ to 5.5 V , $V_{\text{IN+}} = 12 \text{ V}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		± 0.3	± 5	$\mu\text{V}/\text{V}$	
I_B	Input bias current	I_{B+} , I_{B-}		115		μA	
I_{OS}	Input offset current	$V_{\text{SENSE}} = 0 \text{ mV}$		± 0.01		μA	
OUTPUT							
G	Gain	A1 versions		20		V/V	
		A2 versions		50			
		A3 versions		100			
Gain error		$V_{\text{OUT}} = 0.5 \text{ V}$ to $V_S - 0.5 \text{ V}$, A1 versions		$\pm 0.02\%$	$\pm 0.075\%$		
		$V_{\text{OUT}} = 0.5 \text{ V}$ to $V_S - 0.5 \text{ V}$, A2 versions		$\pm 0.05\%$	$\pm 0.1\%$		
		$V_{\text{OUT}} = 0.5 \text{ V}$ to $V_S - 0.5 \text{ V}$, A3 versions		$\pm 0.1\%$	$\pm 0.15\%$		
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		3	10	ppm/ $^\circ\text{C}$	
Nonlinearity error		$V_{\text{OUT}} = 0.5 \text{ V}$ to $V_S - 0.5 \text{ V}$		$\pm 0.01\%$			
Maximum capacitive load		No sustained oscillation		500		pF	
VOLTAGE OUTPUT							
Swing to V_S power-supply rail		$R_L = 10 \text{ k}\Omega$ to GND, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	$V_S - 0.05$	$V_S - 0.1$	30	V	
Swing to GND		$R_L = 10 \text{ k}\Omega$ to GND, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	$V_{\text{GND}} + 15$	$V_{\text{GND}} + 30$	30	mV	
FREQUENCY RESPONSE							
BW	Bandwidth	A1 versions, $C_{\text{OUT}} = 500 \text{ pF}$		550		kHz	
		A2 versions, $C_{\text{OUT}} = 500 \text{ pF}$		440			
		A3 versions, $C_{\text{OUT}} = 500 \text{ pF}$		400			
SR	Slew rate			4		$\text{V}/\mu\text{s}$	
NOISE, RTI⁽¹⁾							
Voltage noise density				30	$\text{nV}/\sqrt{\text{Hz}}$		

(1) RTI = referred-to-input.

Electrical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_{\text{REF}} = V_S / 2$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, $V_{\text{LIMIT1}} = 3 \text{ V}$, and $V_{\text{LIMIT2}} = 3 \text{ V}$ (INA302) or $V_{\text{LIMIT2}} = 2 \text{ V}$ (INA303) (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
COMPARATOR							
t_p	Total alert propagation delay	Comparator 1, input overdrive = 1 mV	0.6	1		μs	
		Comparator 2, input overdrive = 1 mV, delay = 100 k Ω to V_S	1.25	2			
Slew-rate-limited t_p		Comparator 1, V_{OUT} step = 0.5 V to 4.5 V, $V_{\text{LIMIT}} = 4 \text{ V}$	1	1.5		μs	
		Comparator 2 (INA302), V_{OUT} step = 0.5 V to 4.5 V, $V_{\text{LIMIT}} = 4 \text{ V}$, delay = 100 k Ω to V_S	1.5	2.5			
		Comparator 2 (INA303), V_{OUT} step = 4.5 V to 0.5 V, $V_{\text{LIMIT}} = 1 \text{ V}$, delay = 100 k Ω to V_S	1.5	2.5			
I_{LIMIT1}	Limit threshold output current, comparator 1	$T_A = 25^\circ\text{C}$, $V_{\text{LIMIT1}} < V_S - 0.6 \text{ V}$	79.2	80	80.8	μA	
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{\text{LIMIT1}} < V_S - 0.6 \text{ V}$	78.4		81.6		
I_{LIMIT2}	Limit threshold output current, comparator 2	$T_A = 25^\circ\text{C}$, $V_{\text{LIMIT2}} < V_S - 0.6 \text{ V}$	79.7	80	80.4	μA	
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{\text{LIMIT2}} < V_S - 0.6 \text{ V}$	79.2		80.8		
V_{OS}	Offset voltage, both comparators	A1 versions	0.5	3.5		mV	
		A2 versions	0.5	3.5			
		A3 versions	0.5	4.0			
HYS	Hysteresis	comparator 1, comparator 2	100			mV	
Internal programmable delay error		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		4%			
V_{TH}	Delay threshold voltage	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	1.21	1.22	1.23	V	
I_D	Delay charging current	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{\text{DELAY}} = 0.6 \text{ V}$	4.85	5	5.15	μA	
R_D	Delay discharge resistance		70			Ω	
V_{IH}	LATCH1, LATCH2 high-level input voltage	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	1.4	6		V	
V_{IL}	LATCH1, LATCH2 low-level input voltage	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	0	0.4		V	
V_{OL}	Alert low-level output voltage	$I_{\text{OL}} = 3 \text{ mA}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	70	400		mV	
ALERT1, ALERT2 pin leakage input current		$V_{\text{OH}} = 3.3 \text{ V}$	0.1	1		μA	
LATCH1, LATCH2 digital leakage input current		$0 \text{ V} \leq V_{\text{LATCH1}}, V_{\text{LATCH2}} \leq V_S$	1			μA	
POWER SUPPLY							
V_S	Operating supply range	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	2.7	5.5		V	
I_Q	Quiescent current	$T_A = 25^\circ\text{C}$	850	950		μA	
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		1150			
TEMPERATURE RANGE							
Specified range			-40	125		$^\circ\text{C}$	

6.6 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_{\text{REF}} = V_S / 2$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, and $\overline{\text{ALERT1}}, \overline{\text{ALERT2}}$ pullup resistor = $10 \text{ k}\Omega$ (unless otherwise noted)

Population

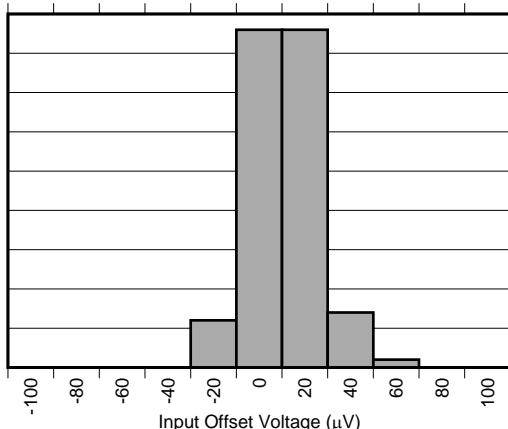


图 1. Input Offset Voltage Distribution (INA30xA1)

Population

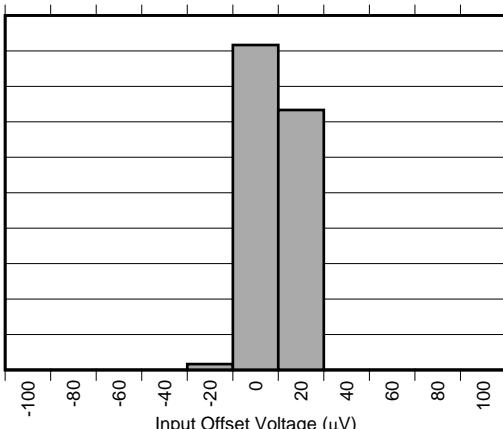


图 2. Input Offset Voltage Distribution (INA30xA2)

Population

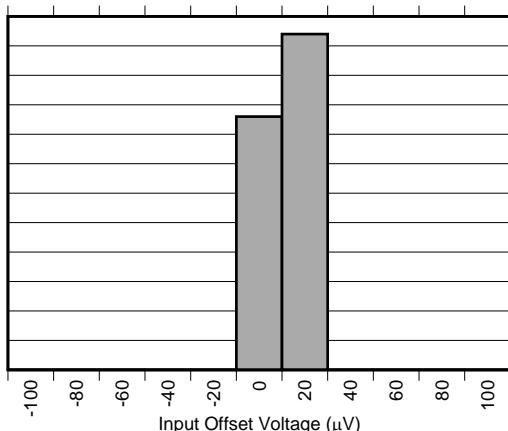


图 3. Input Offset Voltage Distribution (INA30xA3)

Offset Voltage (μV)

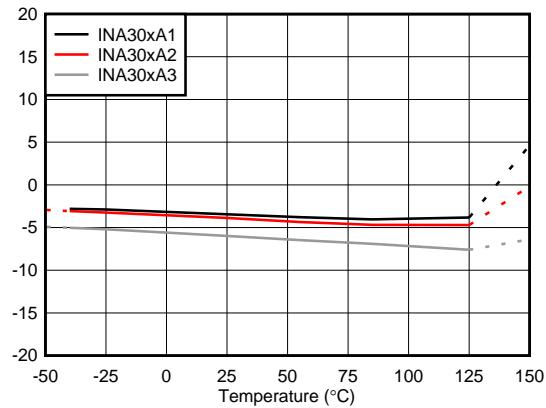


图 4. Input Offset Voltage vs Temperature

Population

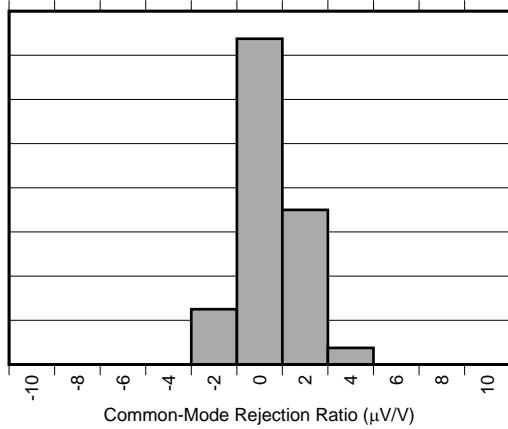


图 5. CMRR Distribution (INA30xA1)

Population

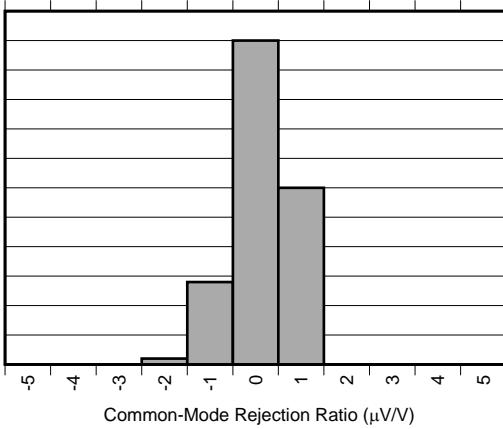
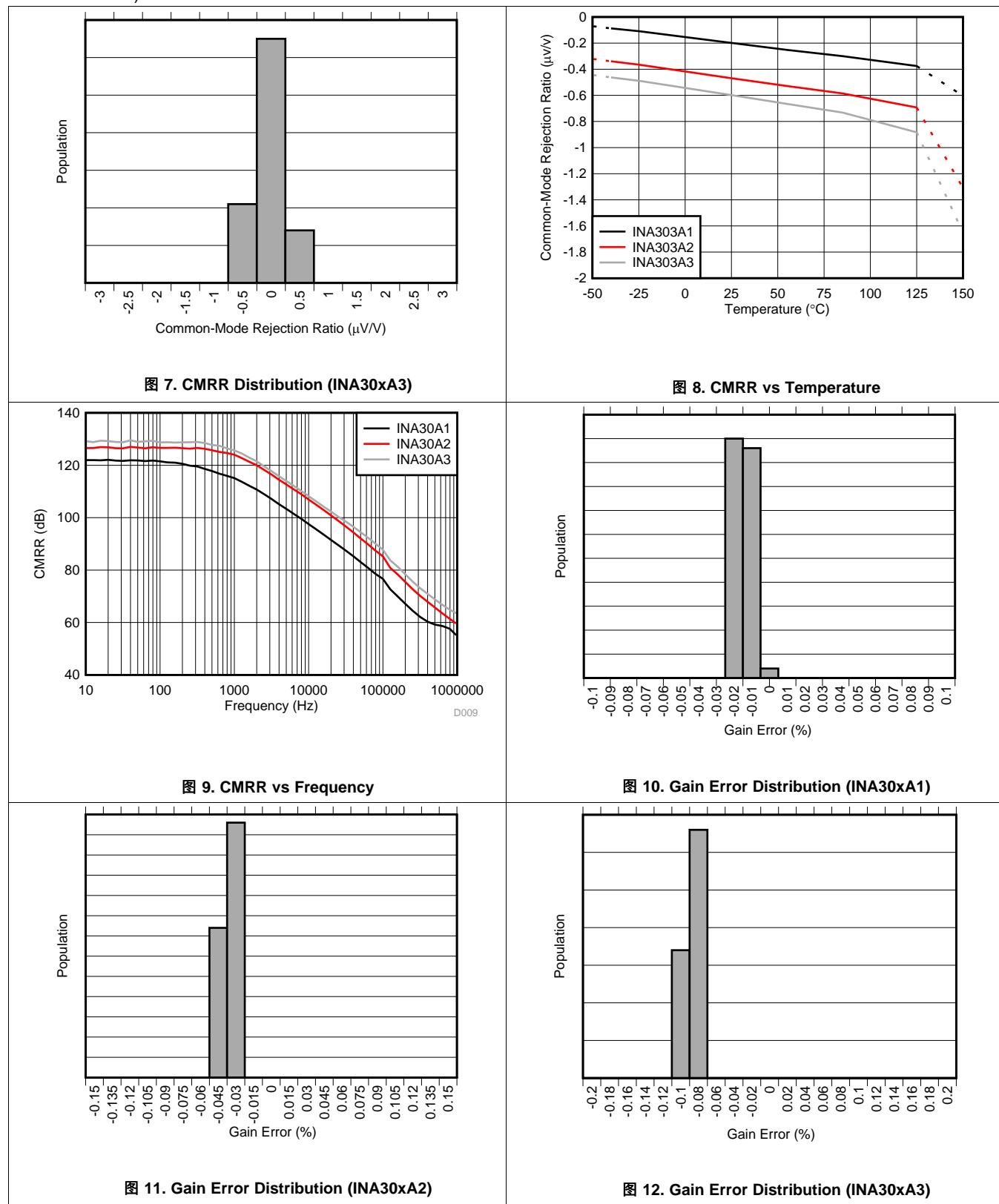


图 6. CMRR Distribution (INA30xA2)

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_{\text{REF}} = V_S / 2$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, and $\overline{\text{ALERT1}}, \overline{\text{ALERT2}}$ pullup resistor = $10 \text{ k}\Omega$ (unless otherwise noted)



Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_{\text{REF}} = V_S / 2$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, and $\overline{\text{ALERT1}}, \overline{\text{ALERT2}}$ pullup resistor = $10 \text{ k}\Omega$ (unless otherwise noted)

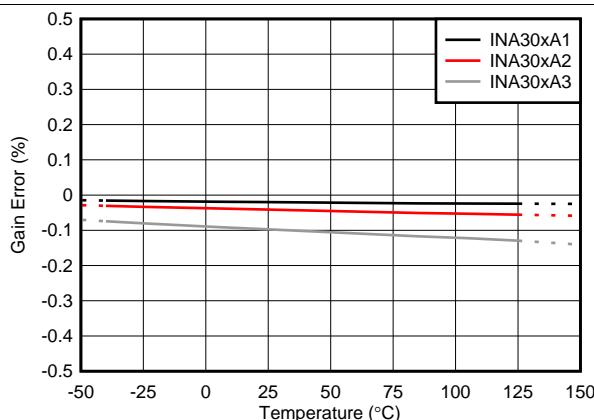


图 13. Gain Error vs Temperature

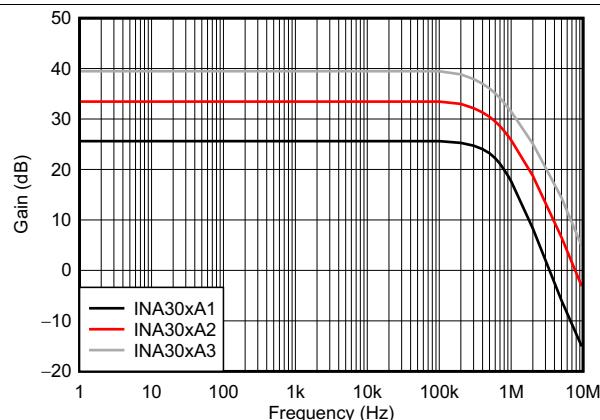


图 14. Gain vs Frequency

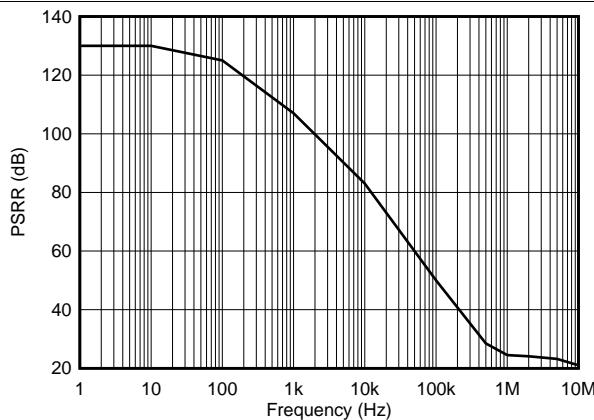


图 15. PSRR vs Frequency

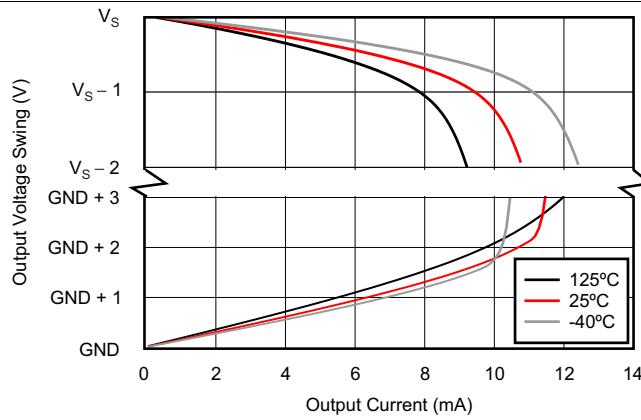


图 16. Output Voltage Swing vs Output Current

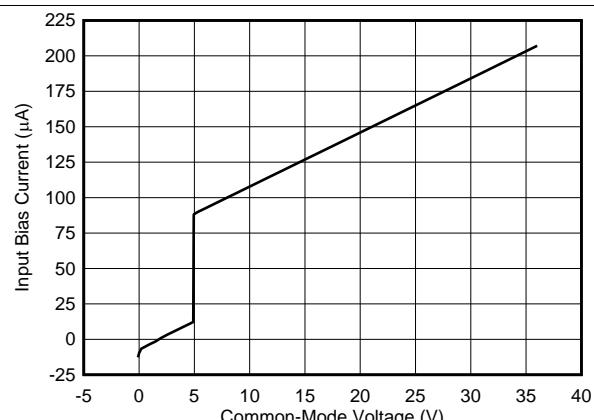


图 17. Input Bias Current vs Common-Mode Voltage
($V_S = 5 \text{ V}$)

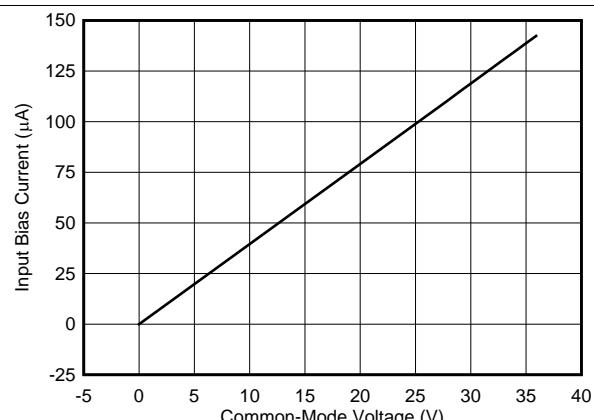


图 18. Input Bias Current vs Common-Mode Voltage
($V_S = 0 \text{ V}$)

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_{\text{REF}} = V_S / 2$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, and $\overline{\text{ALERT1}}, \overline{\text{ALERT2}}$ pullup resistor = $10 \text{ k}\Omega$ (unless otherwise noted)

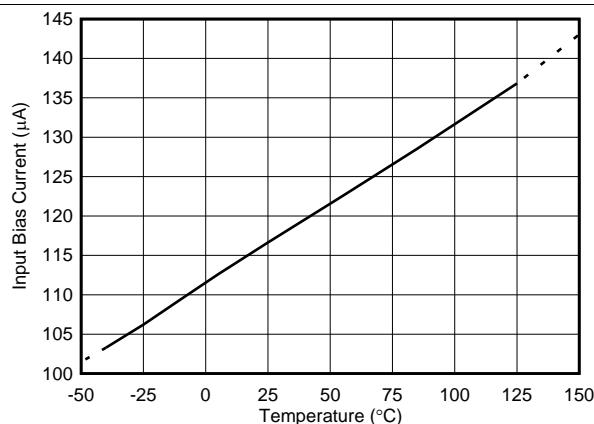


图 19. Input Bias Current vs Temperature

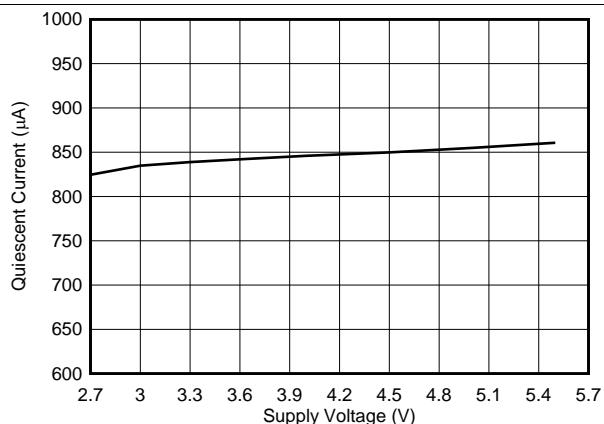


图 20. Quiescent Current vs Supply Voltage

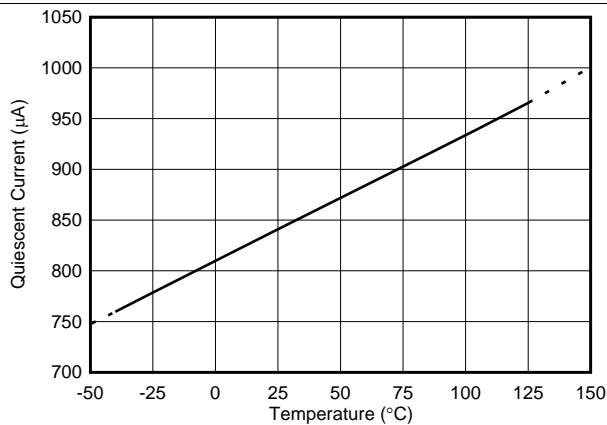


图 21. Quiescent Current vs Temperature

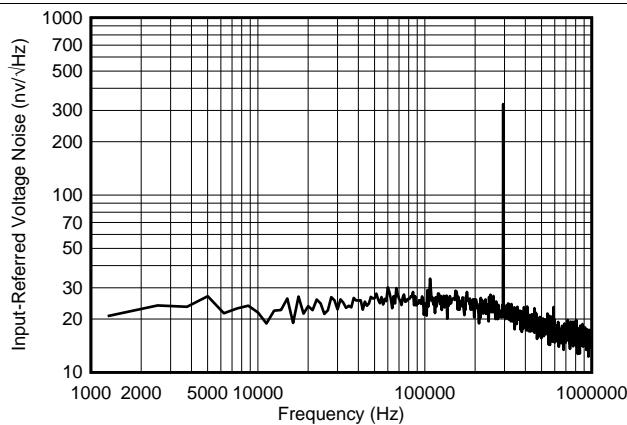


图 22. Input-Referred Voltage Noise vs Frequency

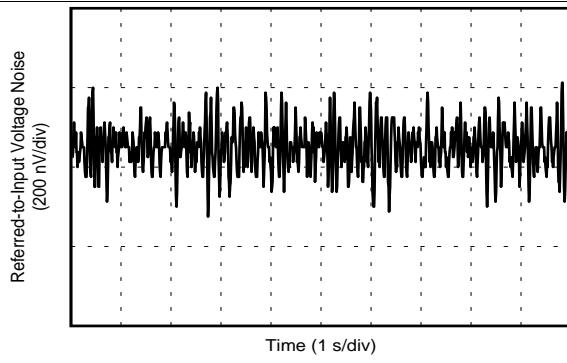


图 23. 0.1-Hz to 10-Hz Voltage Noise (Referred-to-Input)

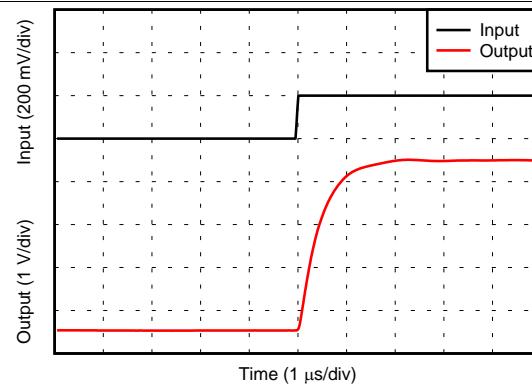


图 24. Voltage Output Rising Step Response (4-V_{PP} Output Step)

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_{\text{REF}} = V_S / 2$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, and $\overline{\text{ALERT1}}, \overline{\text{ALERT2}}$ pullup resistor = $10 \text{ k}\Omega$ (unless otherwise noted)

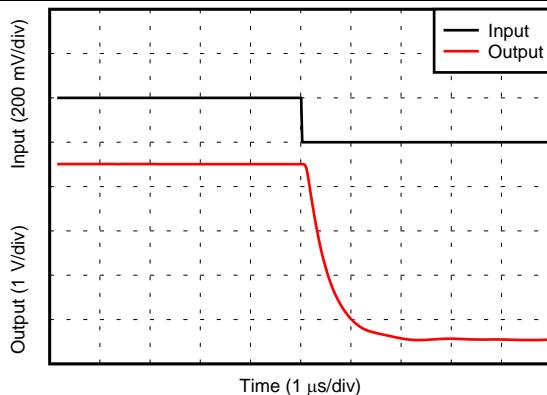


图 25. Voltage Output Falling Step Response
(4-V_{PP} Output Step)

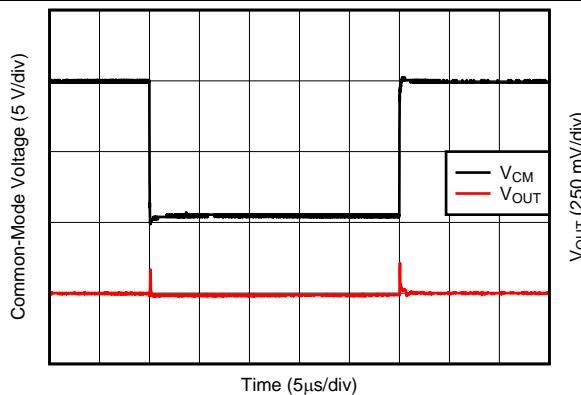


图 26. Common-Mode Voltage Transient Response

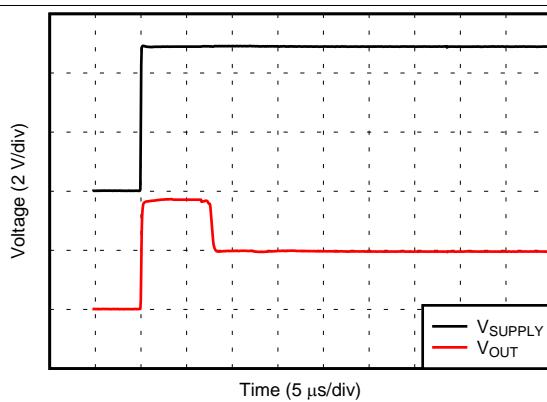


图 27. Start-Up Response

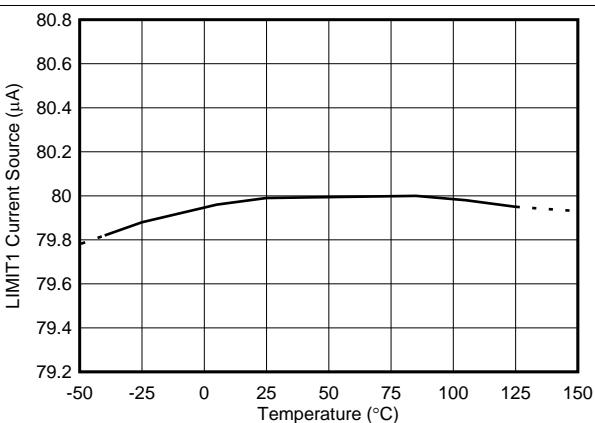


图 28. LIMIT1 Current Source vs Temperature

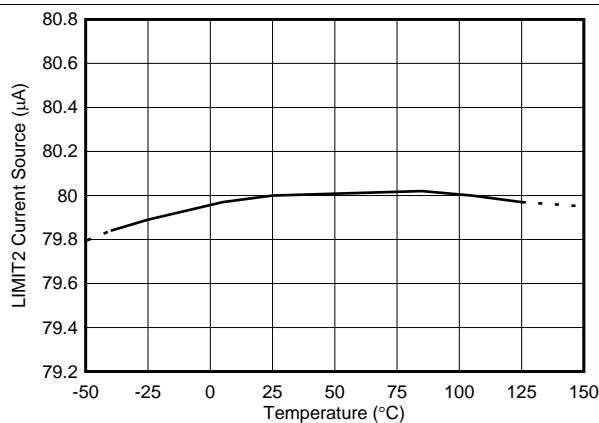


图 29. LIMIT2 Current Source vs Temperature

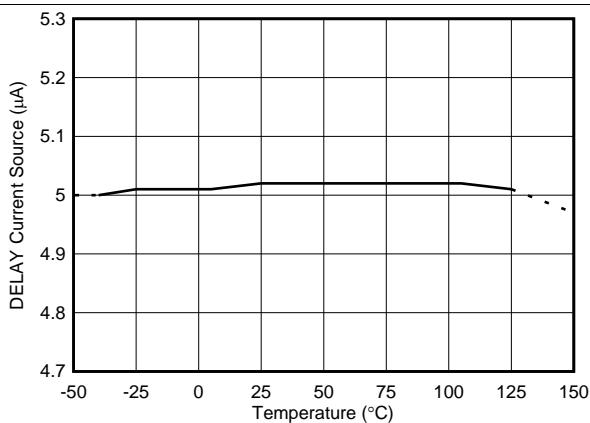
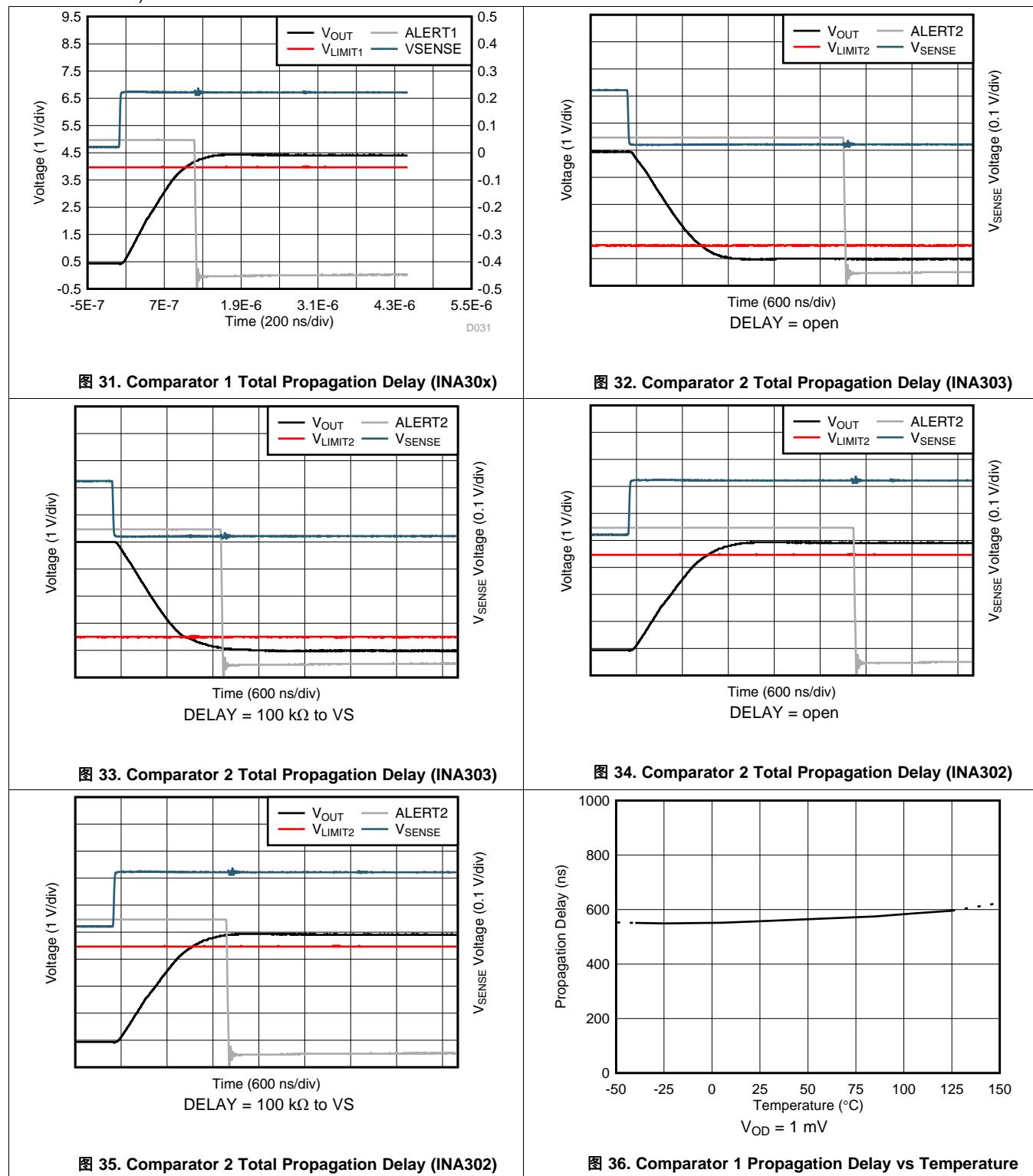


图 30. DELAY Current vs Temperature

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_{\text{REF}} = V_S / 2$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, and $\overline{\text{ALERT1}}, \overline{\text{ALERT2}}$ pullup resistor = $10 \text{ k}\Omega$ (unless otherwise noted)



Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_{\text{REF}} = V_S / 2$, $V_{\text{SENSE}} = 0 \text{ V}$, $V_S = 5 \text{ V}$, $V_{\text{IN+}} = 12 \text{ V}$, and $\overline{\text{ALERT1}}, \overline{\text{ALERT2}}$ pullup resistor = $10 \text{ k}\Omega$ (unless otherwise noted)

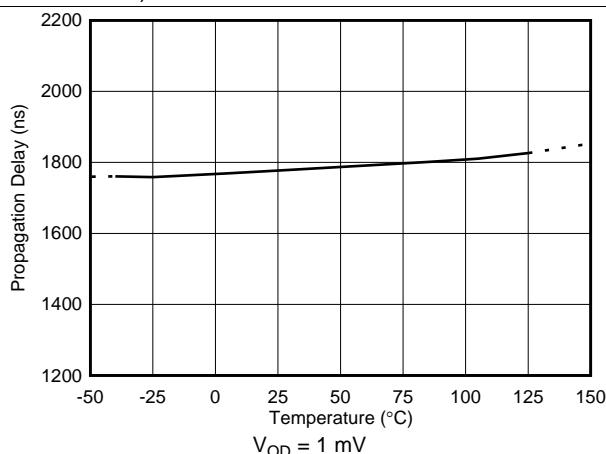


图 37. Comparator 2 Propagation Delay vs Temperature

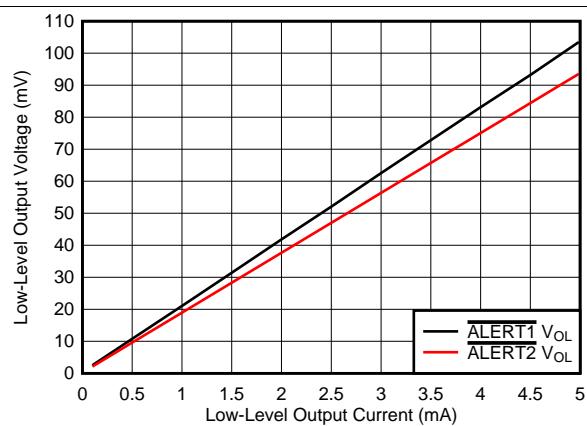


图 38. Comparator Alert V_{OL} vs I_{OL}

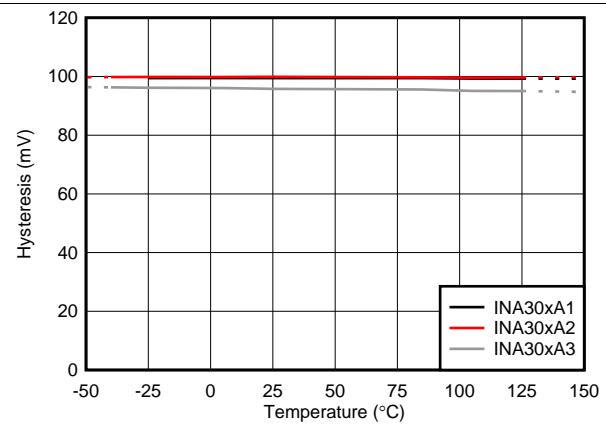


图 39. Comparator 1 Hysteresis vs Temperature

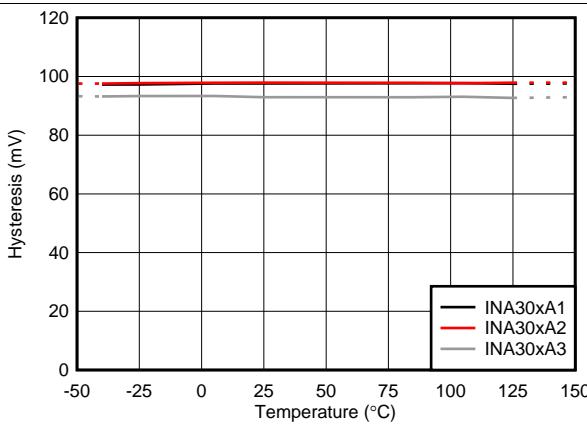


图 40. Comparator 2 Hysteresis vs Temperature

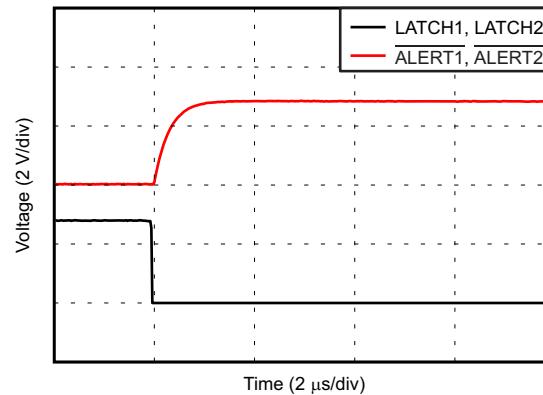


图 41. Comparator Latch Response

7 Detailed Description

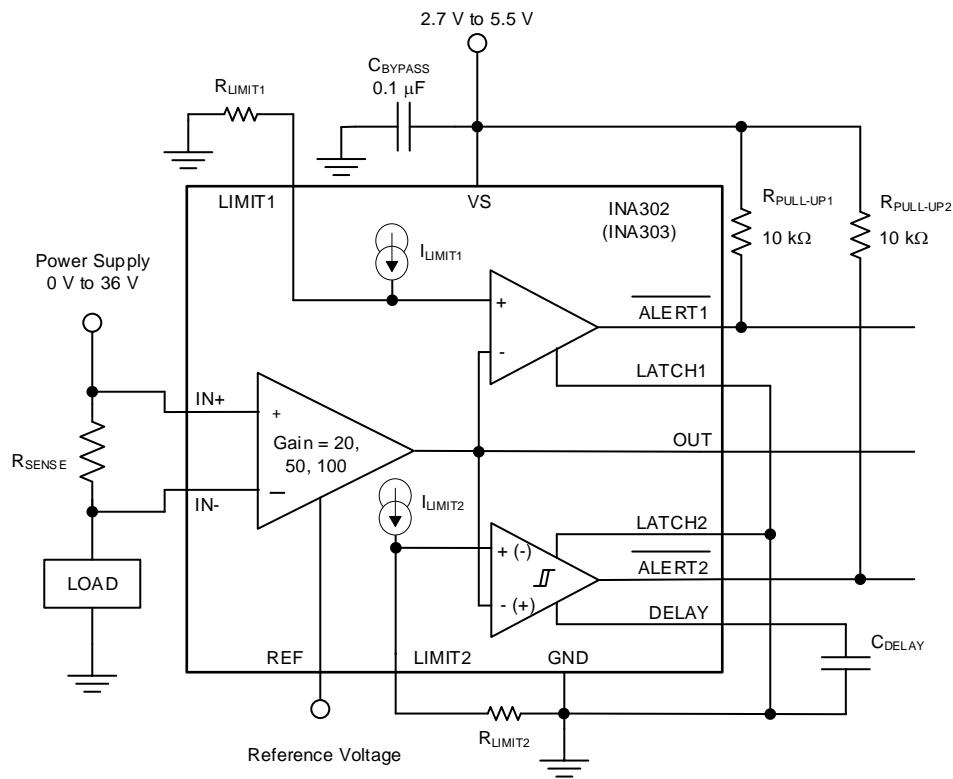
7.1 Overview

The INA30x features a zero-drift, 36-V, common-mode, bidirectional, current-sensing amplifier and two high-speed comparators that can detect multiple out-of-range current conditions. The specially designed, current-sensing amplifier can be used in both low-side or high-side applications where common-mode voltages far exceed the supply voltage of the device. Currents are measured by accurately sensing voltages developed across current-sensing resistors (also known as *current-shunt resistors*). Current can be measured on input voltage rails as high as 36 V, and the device can be powered from supply voltages as low as 2.7 V.

The zero-drift topology enables high-precision measurements with maximum input offset voltages as low as 30 μ V (max) with a temperature contribution of only 0.25 μ V/ $^{\circ}$ C (max) over the full temperature range of -40° C to $+125^{\circ}$ C. The low total offset voltage of the INA302 enables smaller current-sense resistor values to be used, improving power-efficiency without sacrificing measurement accuracy resulting from the smaller input signal.

Both the INA302 and INA303 use a single external resistor to set each out-of-range threshold. The INA302 allows for two overcurrent thresholds and the INA303 allows for both an under- and overcurrent threshold. The response time of the ALERT1 threshold is fixed and is less than 1 μ s. The response time of the ALERT2 threshold can be set with an external capacitor. The combination of a precision current-sense amplifier with onboard comparators creates a highly-accurate solution that is capable of fast detection of multiple out-of-range conditions. The ability to detect when currents are out-of-range allows the system to take corrective actions to prevent potential component or system-wide damage.

7.2 Functional Block Diagram



Copyright © 2017, Texas Instruments Incorporated

7.3 Feature Description

7.3.1 Bidirectional Current Sensing and Out-of-Range Detection

The INA302 and INA303 can sense current flow through a sense resistor in both directions. The bidirectional current-sensing capability is achieved by applying a voltage at the REF pin to offset the output voltage. A positive differential voltage sensed at the inputs results in an output voltage that is above the applied reference voltage; likewise, a negative differential voltage at the inputs results in output voltage that is below the applied reference voltage. The equation for the output voltage of the current-sense amplifier is shown in [公式 1](#).

$$V_{OUT} = (I_{LOAD} \times R_{SENSE} \times GAIN) + V_{REF}$$

where

- I_{LOAD} is the load current to be monitored
- R_{SENSE} is the current-sense resistor
- GAIN is the gain option of the device selected and
- V_{REF} is the voltage applied to the REF pin

(1)

The INA303 can detect when negative currents are out-of-range by setting a voltage at the LIMIT2 pin that is below the applied reference voltage. The limit voltage can be set with an external resistor or externally driven by a voltage source or digital-to-analog converter (DAC); see the [Setting Alert Thresholds](#) section for additional information. A typical application using the INA303 to detect negative overcurrent conditions is illustrated in the [Typical Application](#) section.

7.3.2 Alert Outputs

Both \overline{ALERT}_x pins are active-low, open-drain outputs that pull low when the sensed current is detected to be out-of-range. Both open-drain \overline{ALERT}_x pins require an external pullup resistor to an external supply. The external supply for the pullup voltage can exceed the supply voltage, V_S , but is restricted from operating above 5.5 V. The pullup resistance is selected based on the capacitive load and required rise time; however, a 10-k Ω resistor value is typically sufficient for most applications. The response time of the \overline{ALERT}_1 output to an out-of-range event is less than 1 μ s, and the response time of the \overline{ALERT}_2 output is proportional to the value of the external C_{DELAY} capacitor. The equation to calculate the delay time for the \overline{ALERT}_2 output is given in [公式 2](#):

$$t_{DELAY} = \begin{cases} 1.5 \mu\text{s} & \text{If } C_{DELAY} \geq 47 \text{ pF} \\ \frac{C_{DELAY} \times V_{TH}}{I_D} + 2.5 \mu\text{s} & \text{If } C_{DELAY} < 47 \text{ pF} \end{cases}$$

where,

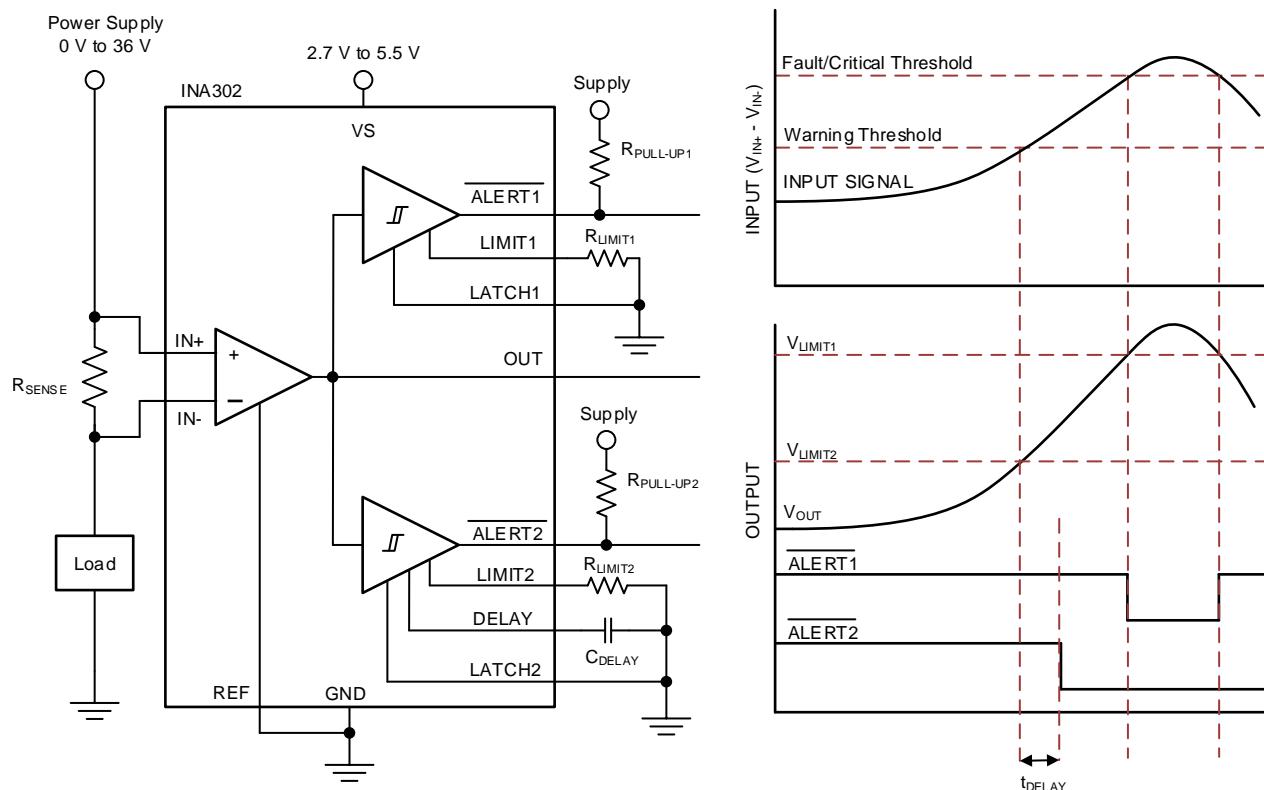
- C_{DELAY} is the external delay capacitor
- V_{TH} is the delay threshold voltage and
- I_D is the $DELAY$ pin current for comparator 2

(2)

For example, if a delay time of 10 μ s is desired, the calculated value for C_{DELAY} is 492 pF. The closest standard capacitor value to the calculated value is 500 pF. If a delay time greater than 2.5 μ s on the \overline{ALERT}_2 output is not needed, the C_{DELAY} capacitor can be omitted. To achieve minimum delay on the \overline{ALERT}_2 output, connecting a 100-k Ω resistor from the $DELAY$ pin to the V_S pin is recommended. Both comparators in the INA30x have hysteresis to avoid oscillations in the \overline{ALERT}_x outputs. The effect hysteresis has on the comparator behavior is described in the [Hysteresis](#) section.

Feature Description (接下页)

图 42 显示了内部比较器的警报输出响应。当电流感测放大器的输出电压低于任一限位引脚上的电压时，两个 ALERT_X 输出均处于默认高电平状态。当电流感测放大器输出大于由 LIMIT2 引脚设置的阈值电压时，ALERT2 输出在由外部延时电容设置的延时时间后变低。较低的过电流阈值通常被称为 *overcurrent warning threshold*。如果电流继续上升，直到电流感测放大器输出电压超过由 LIMIT1 引脚设置的阈值电压，则 ALERT1 输出变为活动状态并立即变低。低电压的 ALERT1 指示测量信号在放大器输入处已超过预定阈值，表示过电流条件已发生。较高的阈值通常被称为 *fault* 或 *system critical threshold*。系统通常在电流超过此阈值时启动保护程序（例如系统关机）。

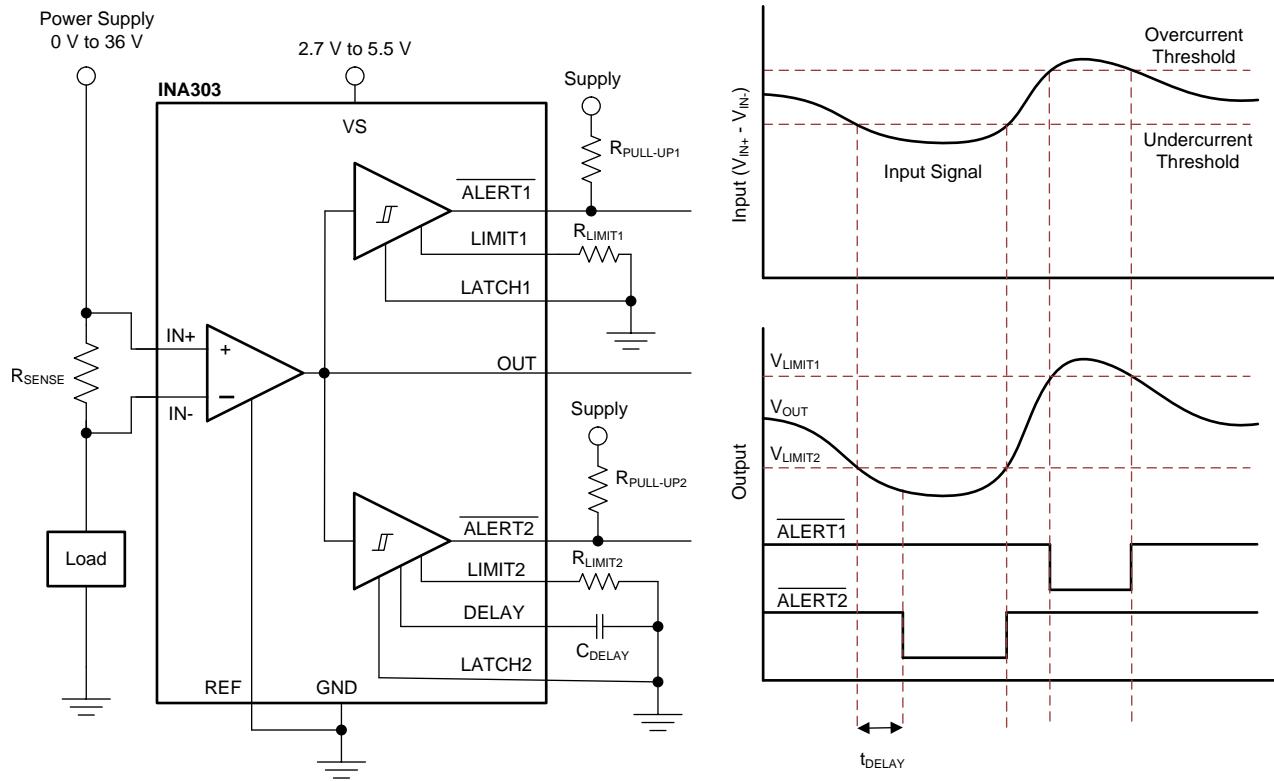


Copyright © 2017, Texas Instruments Incorporated

图 42. Out-of-Range Alert Responses for the INA302

Feature Description (接下页)

图 43 显示了内部比较器的警报输出响应。两个 ALERT_x 输出在默认高状态时，当电流感测放大器的输出电压低于 LIMIT1 引脚上的电压时，或高于 LIMIT2 引脚上的电压时。ALERT1 输出变为低电平，当放大器输入信号超过设置在 LIMIT1 引脚上的阈值时。低电压表示测量信号已超过编程的阈值水平，表示已发生过电流或超出范围条件。当放大器输出电压低于由 LIMIT2 引脚设置的阈值时，ALERT2 输出在外部延迟电容过期后变为低电平。ALERT2 的延迟时间与外部 C_{DELAY} 电容的值成正比，可以通过 [公式 2](#) 计算。

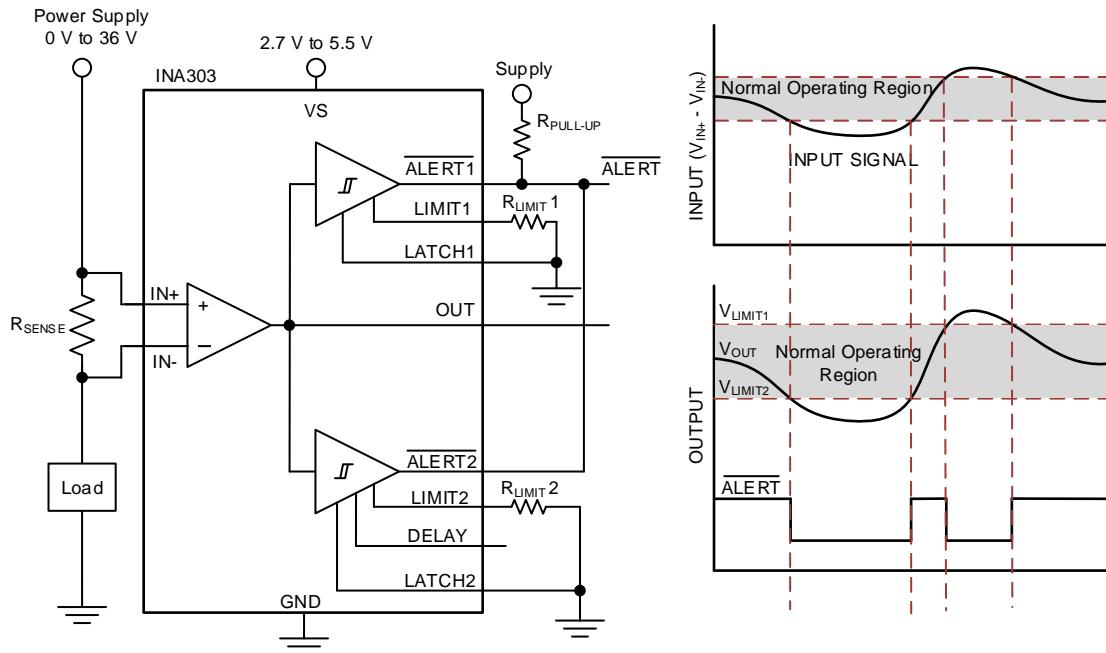


Copyright © 2017, Texas Instruments Incorporated

图 43. Out-of-Range Alert Responses for the INA303

Feature Description (接下页)

图 44 显示了当两个 ALERT_x 引脚连接在一起时，INA303 的警报输出响应。当配置为这种方式时，INA303 可以提供一个单一的信号来指示所感测的电流是否在正常操作带之外或在正常操作窗口内。Both ALERT1 和 ALERT2 输出在警报模式下表现相同。与 ALERT2 不同的是，输出状态的过渡由外部延时电容设置。如果在延时时间到期时没有检测到过流或欠流事件，ALERT2 不会响应。



Copyright © 2017, Texas Instruments Incorporated

图 44. Current Window Comparator Implementation with the INA303

7.3.3 Alert Operating Mode

Each comparator has two output operating modes (transparent and latched) that are selected based on how the LATCH_x pins are connected. These modes determine how the ALERT_x pins respond when an out-of-range condition is removed.

7.3.3.1 Transparent Output Mode

The comparators are set to transparent mode when the corresponding LATCH_x pin is pulled low. When set to the transparent state, the output of the comparators changes and follows the input signal with respect to the programmed alert threshold. For example, when the amplifier output violates the set limit value, the ALERT_x output pin is pulled low. As soon as the differential input signal drops below the alert threshold, the output returns to the default high output state. A common implementation using the device in transparent mode is to connect the ALERT_x pins to a hardware interrupt input on a microcontroller. The ALERT_x pin is pulled low as soon as an out-of-range condition is detected, notifying the microcontroller of the out-of-range condition. The microcontroller begins taking action to address the overcurrent condition because the microcontroller immediately reacts to the alert. There is no need to latch the state of the alert output in this mode of operation because the microcontroller responds as soon as the out-of-range condition occurs.

Feature Description (接下页)

7.3.3.2 Latch Output Mode

Some applications do not have the ability to continuously monitor the state of the ALERT_x pins as described in the Transparent Output Mode section. A typical example of this application is a system that is only able to poll the state of the ALERT_x pins periodically. If the device is set to transparent mode in this type of application, then the transition of the ALERT_x pins can be missed if the out-of-range condition is not present during one of these periodic polling events. Latch mode allows the output of the comparators to latch the output of the range condition so that the transition of the ALERT_x pins is not missed when the status of the comparator ALERT_x pins is polled.

The device is placed into either transparent or latched state based on the voltage applied to the corresponding LATCH_x pin, as shown in [表 1](#). The difference between latch mode and transparent mode is how the alert output responds when an overcurrent condition is removed. In transparent mode (LATCH1, LATCH2 = low), when the differential input signal drops to within normal operating range, the ALERT_x pin returns to the default high setting to indicate that the overcurrent event has ended.

表 1. Output Mode Settings

OUTPUT MODE	LATCH _x PINS SETTINGS
ALERT _x transparent mode	LATCH _x = low
ALERT _x latch mode	LATCH _x = high

In latch mode (LATCH_x = high), when an out-of-range condition is detected and the corresponding ALERT_x pin is pulled low; the ALERT_x pin does not return to the default high state when the out-of-range condition is removed. In order to clear the alert, the corresponding LATCH_x pin must be pulled low for at least 100 ns. Pulling the LATCH_x pins low allows the corresponding ALERT_x pin to return to the default high level, provided the out-of-range condition is no longer present. If the out-of-range condition is still present when the LATCH_x pins are pulled low, then the corresponding ALERT_x pin remains low. The ALERT_x pins can be cleared (reset to high) by toggling the corresponding LATCH_x pin when the alert condition is detected by the system controller.

The latch and transparent modes are illustrated in [图 45](#). As illustrated in this figure, at time t_1 the current-sense amplifier exceeds the limit threshold. During this time the LATCH1 pin is toggled with no affect to the ALERT1 output. The state of the LATCH1 pin only matters when the output of the current-sense amplifier returns to the normal operating region, as shown at t_2 . At this time the LATCH1 pin is high and the overcurrent condition is latched on the ALERT1 output. As shown in the time interval between t_2 and t_3 , the latch condition is cleared when the LATCH_x pin is pulled low. At time t_4 , the LATCH1 pin is already pulled low when the amplifier output drops below the limit threshold for the second time. The device is set to transparent mode at this point and the ALERT1 pin is pulled back high as soon as the output of the current-sense amplifier drops below the alert threshold.

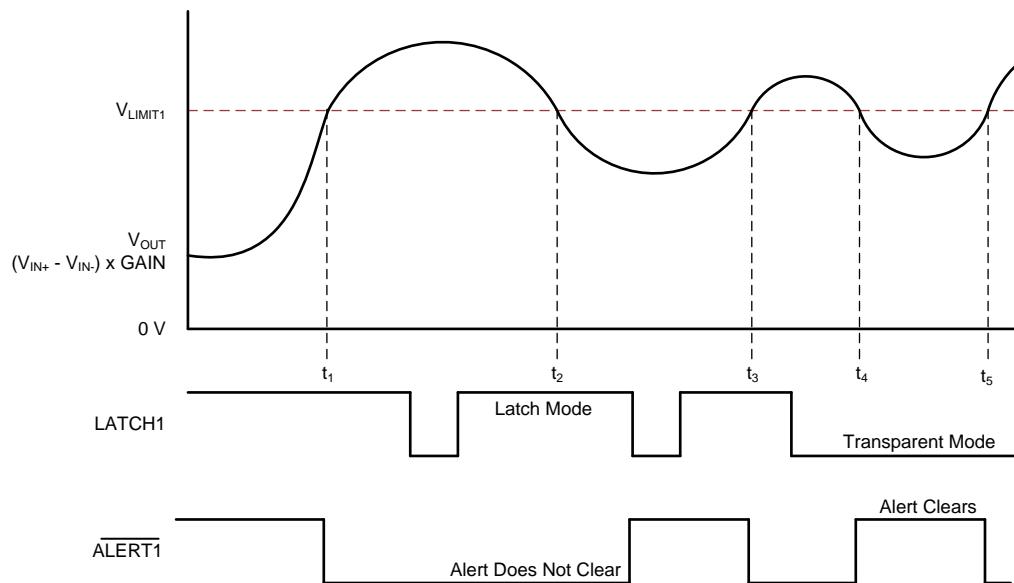


图 45. Transparent versus Latch Mode

7.3.4 Setting Alert Thresholds

The INA30x family of devices determines if an out-of-range event is present by comparing the amplifier output voltage to the voltage at the corresponding LIMITx pin. The threshold voltage for the LIMITx pins can be set using a single external resistor or by connecting an external voltage source to each pin. The INA302 allows setting limits for two overcurrent conditions. Generally, the lower overcurrent threshold is referred to as a *warning limit* and the higher overcurrent threshold is referred to as the *critical* or *fault limit*. The INA303 allows setting thresholds to detect both under- and overcurrent limit conditions.

7.3.4.1 Resistor-Controlled Current Limit

The typical approach to set the limit threshold voltage is to connect resistors from the two LIMITx pins to ground. The voltage developed across the R_{LIMIT1} , R_{LIMIT2} resistors represents the desired fault current value at which the corresponding ALERTx pin becomes active. The values for the R_{LIMIT1} , R_{LIMIT2} resistors can be calculated using 公式 3:

$$R_{LIMIT} = \frac{(I_{TRIP} \times R_{SENSE} \times GAIN) + V_{REF}}{I_{LIMIT}}$$

where,

- I_{TRIP} is the desired out-of-range current threshold
- R_{SENSE} is the current-sensing resistor
- GAIN is the gain option of the device selected
- V_{REF} is the voltage applied to the REF pin
- I_{LIMIT} is the limit threshold output current for the selected comparator, typically 80 μ A

注

When solving for the value of R_{LIMIT} , the voltage at the corresponding LIMITx pin as determined by the product of R_{LIMIT} and I_{LIMIT} must not exceed the compliance voltage of $VS - 0.6$ V.

7.3.4.1.1 Resistor-Controlled Current Limit: Example

For example, if the current level indicating an out-of-range condition (I_{TRIP}) is 20 A and the current-sense resistor value (R_{SENSE}) is 10 mΩ, then the input threshold signal is 200 mV. The INA302A1 has a gain of 20, so the resulting output voltage at the 20-A input condition is 4 V at the output of the current-sense amplifier when the REF pin is grounded. The value for R_{LIMIT} is selected to allow the device to detect this 20-A threshold, indicating that an overcurrent event has occurred. When the INA302 detects this out-of-range condition, the \overline{ALERTx} pin asserts and pulls low. For this example, the value of R_{LIMIT} to detect a 4-V level is calculated to be 50 kΩ.

7.3.4.2 Voltage-Source-Controlled Current Limit

The second method for setting the out-of-range threshold is to directly drive the $LIMITx$ pins with a programmable DAC or other external voltage source. The benefit of this method is the ability to adjust the current-limit threshold to account for different threshold voltages used for different system operating conditions. For example, this method can be used in a system with one current-limit threshold level that must be monitored during a power-up sequence but different threshold levels must be monitored during other system operating modes.

The voltage applied at the $LIMITx$ pins sets the threshold voltage for out-of-range detection. The value of the voltage for a given desired current trip point can be calculated using [公式 4](#):

$$V_{SOURCE} = (I_{TRIP} \times R_{SENSE} \times GAIN) + V_{REF}$$

where,

- I_{TRIP} is the desired out-of-range current threshold
- R_{SENSE} is the current-sensing resistor
- GAIN is the gain option of the device selected
- V_{REF} is the voltage applied to the REF pin

(4)

注

The maximum voltage that can be applied to the $LIMIT2$ pin is $VS - 0.6$ V and the maximum voltage that can be applied to the $LIMIT1$ pin must not exceed VS .

7.3.5 Selecting a Current-Sensing Resistor (R_{SENSE})

Selecting the value of this current-sensing resistor is based primarily on two factors: the required accuracy of the current measurement and the allowable power dissipation across the current-sensing resistor. Larger voltages developed across this resistor allow for more accurate measurements to be made. Amplifiers have fixed internal errors that are largely dominated by the inherent input offset voltage. When the input signal decreases, these fixed internal amplifier errors become a larger portion of the measurement and increase the uncertainty in the measurement accuracy. When the input signal increases, the measurement uncertainty is reduced because the fixed errors are a smaller percentage of the signal being measured. Therefore, the use of larger-value, current-sensing resistors inherently improves measurement accuracy.

However, a system design trade-off must be evaluated through the use of larger input signals for improving measurement accuracy. Increasing the current-sense resistor value results in an increase in power dissipation across the current-sensing resistor. Increasing the value of the current-shunt resistor increases the differential voltage developed across the resistor when current passes through the component. This increase in voltage across the resistor increases the power that the resistor must be able to dissipate. Decreasing the value of the current-shunt resistor value reduces the power dissipation requirements of the resistor, but increases the measurement errors resulting from the decreased input signal. Selecting the optimal value for the shunt resistor requires factoring both the accuracy requirement for the specific application and the allowable power dissipation of this component.

An increasing number of very low ohmic-value resistors are becoming more widely available with values reaching down as low as 200 μΩ or lower with power dissipations of up to 5 W that enable large currents to be accurately monitored with sensing resistors.

7.3.5.1 Selecting a Current-Sensing Resistor: Example

In this example, the trade-offs involved in selecting a current-sensing resistor are discussed. This example requires 2.5% accuracy for detecting a 10-A overcurrent event where only 250 mW is allowable for the dissipation across the current-sensing resistor at the full-scale current level. Although the maximum power dissipation is defined as 250 mW, a lower dissipation is preferred to improve system efficiency. Some initial assumptions are made that are used in this example: the limit-setting resistor (R_{LIMIT}) is a 1% component and the maximum tolerance specification for the internal threshold setting current source (1%) is used. Given the total error budget of 2.5%, up to 0.5% of error can be attributed to the measurement error of the device under these conditions.

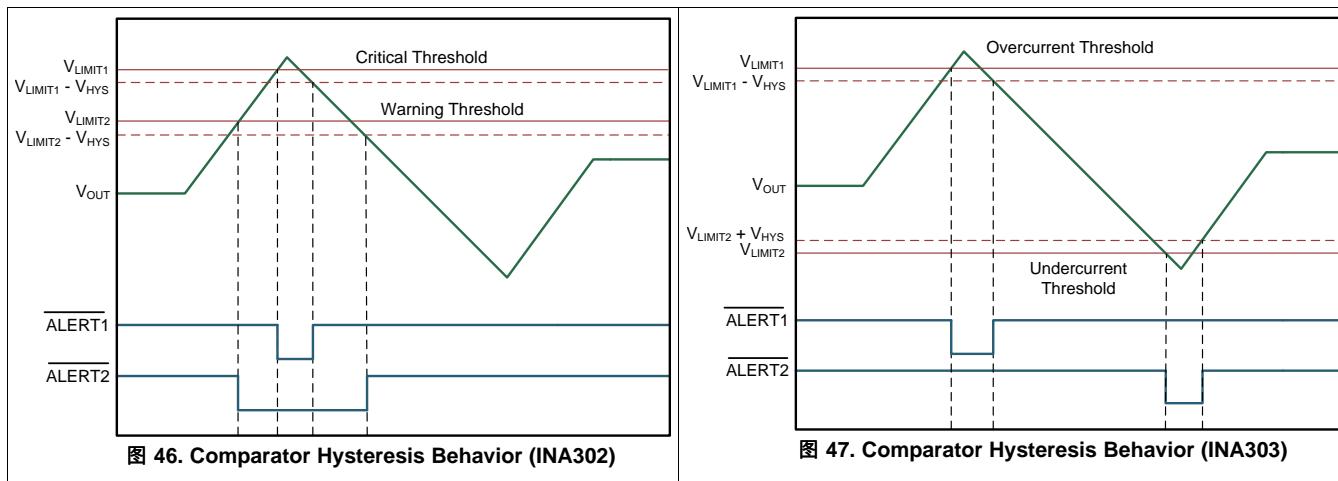
As shown in [表 2](#), the maximum value calculated for the current-sensing resistor with these requirements is 2.5 mΩ. Although this value satisfies the maximum power dissipation requirement of 250 mW, headroom is available from the 2.5% maximum total overcurrent detection error to reduce the value of the current-sensing resistor and to further reduce power dissipation. Selecting a 1.5-mΩ, current-sensing resistor value offers a good tradeoff for reducing the power dissipation in this scenario by approximately 40% and stays within the accuracy region.

表 2. Calculating the Current-Sensing Resistor, R_{SENSE}

PARAMETER	EQUATION	VALUE	UNIT
DESIGN TARGETS			
I_{MAX}	Maximum current	10	A
P_{D_MAX}	Maximum allowable power dissipation	250	mW
	Allowable current threshold accuracy	2.5%	
DEVICE PARAMETERS			
V_{OS}	Offset voltage	30	μV
E_G	Gain error	0.15%	
CALCULATIONS			
R_{SENSE_MAX}	Maximum allowable R_{SENSE}	P_{D_MAX} / I_{MAX}^2	mΩ
V_{OS_ERROR}	Initial offset voltage error	$(V_{OS} / (R_{SENSE_MAX} \times I_{MAX}) \times 100$	0.12%
$ERROR_{TOTAL}$	Total measurement error	$\sqrt{(V_{OS_ERROR}^2 + E_G^2)}$	0.19%
$ERROR_{INITIAL}$	Initial threshold error	$I_{LIMIT} \text{ tolerance} + R_{LIMIT} \text{ tolerance}$	2%
$ERROR_{AVAILABLE}$	Maximum allowable measurement error	Maximum error – $ERROR_{INITIAL}$	1%
$V_{OS_ERROR_MAX}$	Maximum allowable offset error	$\sqrt{(ERROR_{AVAILABLE}^2 - E_G^2)}$	0.48%
V_{DIFF_MIN}	Minimum differential voltage	$V_{OS} / V_{OS_ERROR_MAX}$ (1%)	mV
R_{SENSE_MIN}	Minimum sense resistor value	V_{DIFF_MIN} / I_{MAX}	mΩ
P_{D_MIN}	Lowest-possible power dissipation	$R_{SENSE_MIN} \times I_{MAX}^2$	mW

7.3.6 Hysteresis

The hysteresis included in the comparators of the INA302 and INA303 reduces the possibility of oscillations in the alert outputs when the measured signal level is near the overlimit threshold level. For overrange events, the corresponding ALERTx pin is asserted when the output voltage (V_{OUT}) exceeds the threshold set at either LIMITx pin. The output voltage must drop below the LIMITx pin threshold voltage by the hysteresis value in order for the ALERTx pin to deassert and return to the nominal high state. Likewise for underrange events, the corresponding ALERTx pin is also pulled low when the output voltage drops below the threshold set by either LIMITx pin. The ALERTx pin is released when the output voltage of the current-sense amplifier rises above the set threshold plus hysteresis. Hysteresis functionality for both over- and underrange events is shown in [图 46](#) and [图 47](#) for the INA302 and INA303, respectively.



7.4 Device Functional Modes

7.4.1 Input Filtering

The integrated comparators in the INA302 and INA303 are very accurate in detecting out-of-range events because of their low offset voltage; however, noise present at the input of the current-sense amplifier and noise internal to the device can make the offset appear larger than specified. The most obvious effect that external noise can have on the operation of a comparator is to cause a false alert condition. If a comparator detects a large noise transient coupled into the signal, the device can easily falsely interpret this transient as an overrange condition.

Device Functional Modes (接下页)

External filtering can help reduce the amount of noise that reaches the comparator and reduce the likelihood of a false alert from occurring because of external noise. The tradeoff to adding this noise filter is that the alert response time is increased because the input signal and the noise are filtered. [图 48](#) shows the implementation of an input filter for the device.

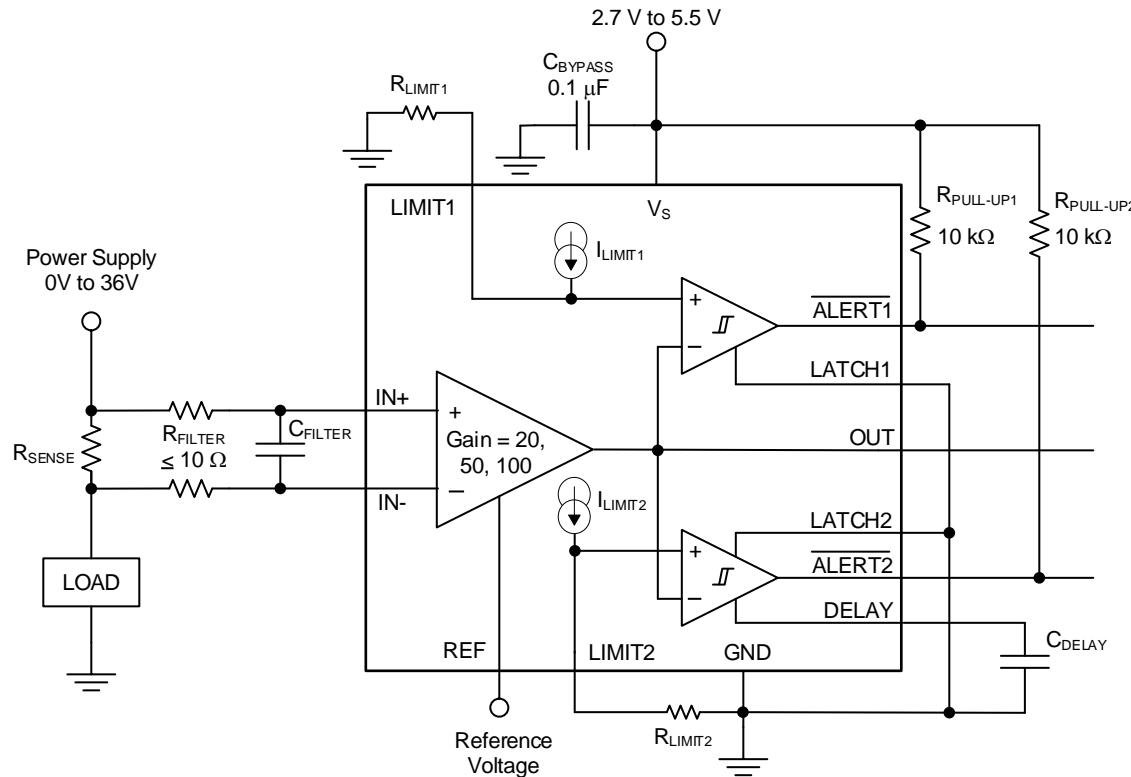


图 48. Input Filter Implementation

Limiting the amount of input resistance used in this filter is important because this resistance can have a significant effect on the input signal that reaches the device input pins by adversely affecting the gain error of the device. A typical system implementation involves placing the current-sensing resistor very near the device so the traces are very short and the trace impedance is very small. This layout helps reduce coupling of additional noise into the measurement. Under these conditions, the characteristics of the input bias currents have minimal effect on device performance.

Device Functional Modes (接下页)

As shown in [图 49](#), the input bias currents increase in opposite directions when the differential input voltage increases. This increase results from the design of the device that allows common-mode input voltages to far exceed the device supply voltage range. When input filter resistors are placed in series with the unequal input bias currents, unequal voltage drops are developed across the input resistors. The difference between these two drops appears as an added signal that (in this case) subtracts from the voltage developed across the current-sensing resistor, thus reducing the signal that reaches the device input pins. Smaller-value input resistors reduce this effect of signal attenuation to allow for a more accurate measurement.

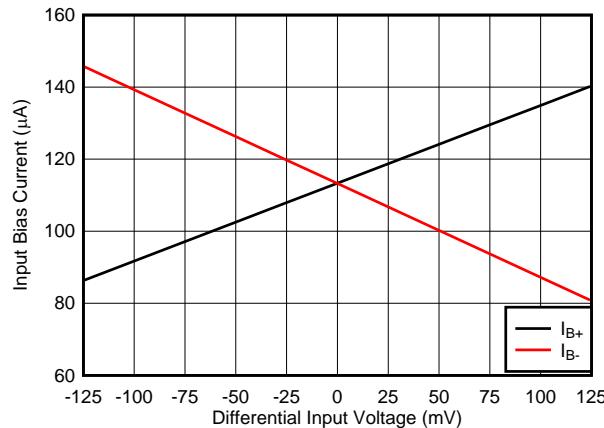
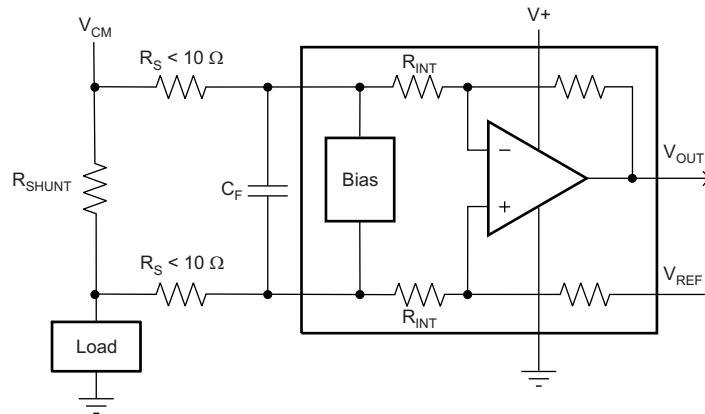


图 49. Input Bias Current vs Differential Input Voltage

The internal bias network shown in [图 50](#) present at the input pins is responsible for the mismatch in input bias currents that is shown in [图 49](#). If additional external series filter resistors are added to the circuit, the mismatch in bias currents results in a mismatch of voltage drops across the filter resistors. This mismatch creates a differential error voltage that subtracts from the voltage developed at the shunt resistor. This error results in a voltage at the device input pins that is different than the voltage developed across the shunt resistor. Without the additional series resistance, the mismatch in input bias currents has little effect on device operation. The amount of error these external filter resistors add to the measurement can be calculated using [公式 6](#) where the gain error factor is calculated using [公式 5](#).



NOTE: Comparators omitted for simplicity.

图 50. Filter at Input Pins

Device Functional Modes (接下页)

The amount of variance in the differential voltage present at the device input relative to the voltage developed at the shunt resistor is based both on the external series resistance value as well as the internal input resistors, R_3 and R_4 (or R_{INT} as illustrated in [图 50](#)). The reduction of the shunt voltage reaching the device input pins appears as a gain error when comparing the output voltage relative to the voltage across the shunt resistor. A factor can be calculated to determine the amount of gain error that is introduced by the addition of external series resistance. The equation used to calculate the expected deviation from the shunt voltage to what is measured at the device input pins is given in [公式 5](#):

$$\text{Gain Error Factor} = \frac{(1250 \times R_{INT})}{(1250 \times R_S) + (1250 \times R_{INT}) + (R_S \times R_{INT})}$$

where:

- R_{INT} is the internal input resistor (R_3 and R_4), and
- R_S is the external series resistance. [\(5\)](#)

With the adjustment factor from [公式 5](#), including the device internal input resistance, this factor varies with each gain version, as shown in [表 3](#). Each individual device gain error factor is shown in [表 4](#).

表 3. Input Resistance

PRODUCT	GAIN	R_{INT} (k Ω)
INA30xA1	20	12.5
INA30xA2	50	5
INA30xA3	100	2.5

表 4. Device Gain Error Factor

PRODUCT	SIMPLIFIED GAIN ERROR FACTOR
INA30xA1	$\frac{12,500}{(11 \times R_S) + 12,500}$
INA30xA2	$\frac{1000}{R_S + 1000}$
INA30xA3	$\frac{2500}{(3 \times R_S) + 2500}$

The gain error that can be expected from the addition of the external series resistors can then be calculated based on [公式 6](#):

$$\text{Gain Error (\%)} = 100 - (100 \times \text{Gain Error Factor}) [\(6\)](#)$$

For example, using an INA302A2 and the corresponding gain error equation from [表 4](#), a series resistance of 10 Ω results in a gain error factor of 0.99. The corresponding gain error is then calculated using [公式 6](#), resulting in a gain error of approximately 1% solely because of the external 10- Ω series resistors.

7.4.2 Using The INA30x With Common-Mode Transients Above 36 V

With a small amount of additional circuitry, the device can be used in circuits subject to transients higher than 36 V. Use only zener diodes or zener-type transient absorbers (sometimes referred to as *transzorbs*). Any other type of transient absorber has an unacceptable time delay. Start by adding a pair of resistors, as shown in [图 51](#), as a working impedance for the zener diode. Keeping these resistors as small as possible is best, preferably 10 Ω or less. Larger values can be used with an additional induced error resulting from a reduced signal that actually reaches the device input pins. Many applications are satisfied with a 10- Ω resistor along with conventional zener diodes of the lowest power rating available because this circuit limits only short-term transients. This combination uses the least amount of board space. These diodes can be found in packages as small as SOT-523 or SOD-523.

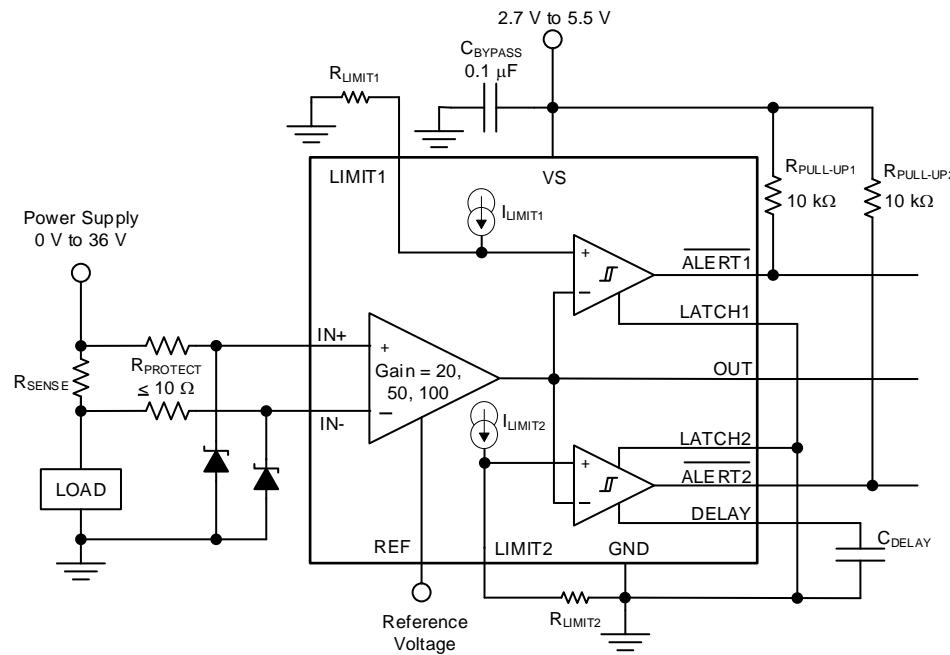


图 51. Transient Protection

8 Application and Implementation

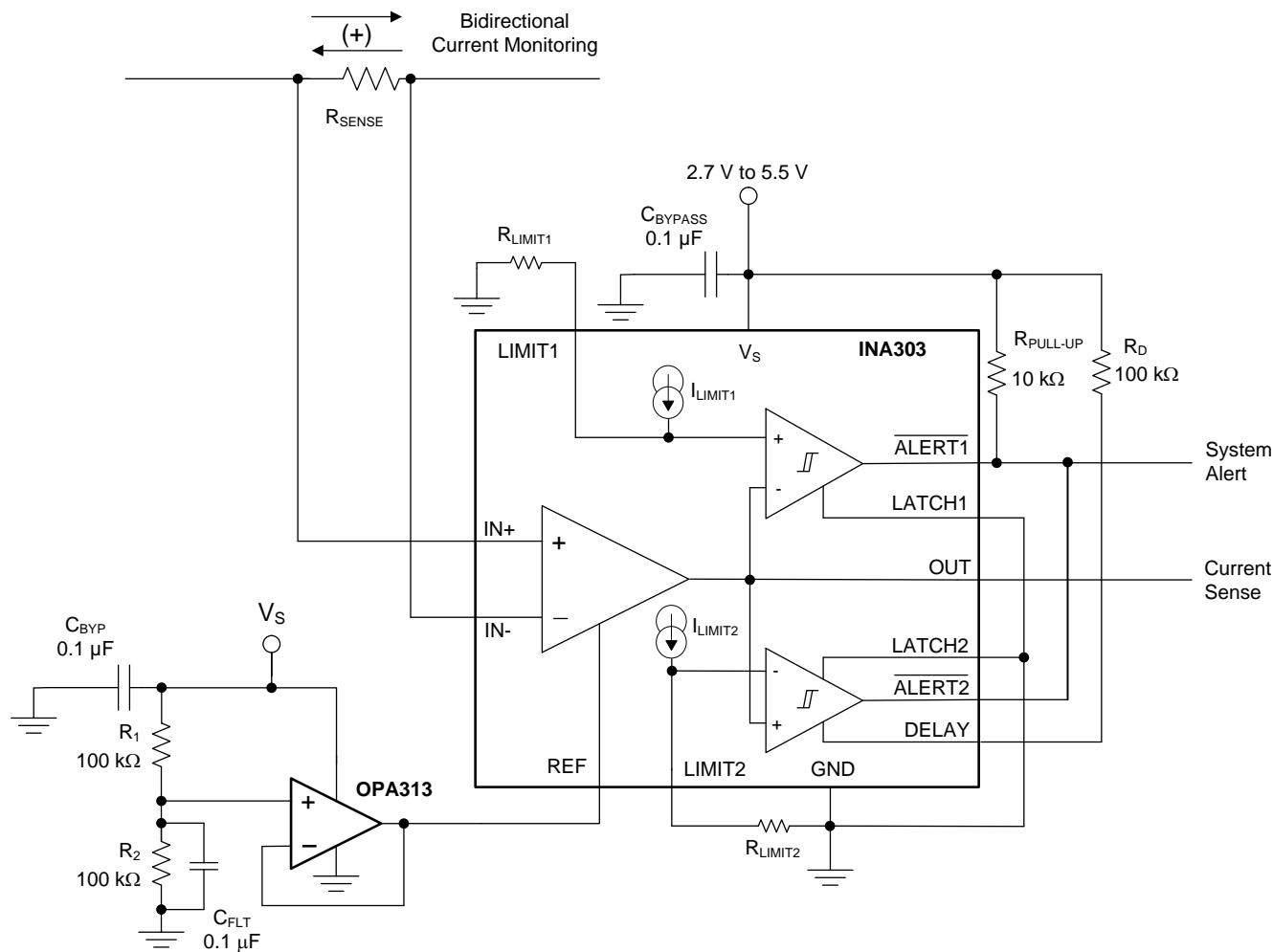
注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The INA302 and INA303 are designed to be easily configured for detecting multiple out-of-range current conditions in an application. This device is capable of monitoring and providing overcurrent detection of bidirectional currents. By using the REF pin of the INA303, both positive and negative overcurrent events can be detected.

8.2 Typical Application



Copyright © 2017, Texas Instruments Incorporated

图 52. Bidirectional Application

Typical Application (接下页)

8.2.1 Design Requirements

To allow for bidirectional monitoring, the INA303 requires a voltage applied to the REF pin. A voltage that is half of the supply voltage is usually preferred to allow for maximum output swing in both the positive and negative current direction. To reduce the errors in the reference voltage, drive the REF pin with a low-impedance source (such as an operational amplifier (op-amp) or external reference). A low-value resistor divider can be used at the expense of quiescent current and accuracy. For this design a single alert output is preferred, so both ALERT1 and ALERT2 are connected together and use a single pullup resistor.

8.2.2 Detailed Design Procedure

To achieve bidirectional monitoring, the reference pin is driven half way between the supply with a resistor divider buffered by an op-amp, as shown in [表 5](#). To reduce the current draw from the supply, 100-k Ω resistors were used to create the divide-by-two voltage divider. The [OPA313](#) was selected to buffer the voltage divider because this device can operate from a single-supply rail with low IQ and offset voltage. To minimize the response time of the ALERT2 output, a 100-k Ω pullup resistor was added from the DELAY pin to the VS pin. Select values for R_{SENSE} , R_{LIMIT2} , and R_{LIMIT1} based on the desired current-sense levels and trip thresholds using the information in the [Resistor-Controlled Current Limit](#) and [Selecting a Current-Sensing Resistor \(\$R_{SENSE}\$ \)](#) sections. For this example, the values of R_{LIMIT1} and R_{LIMIT2} were selected such that the positive and negative overcurrent thresholds are the same. [表 5](#) shows the alert output of the INA303 application circuit with the capability to detect both positive and negative overcurrent conditions.

表 5. Bidirectional Overcurrent Output Status

OVERCURRENT PROTECTION (OCP) STATUS	OUTPUT
Positive overcurrent detection (OCP+)	0
Negative overcurrent detection (OCP-)	0
Normal operation (no OCP)	1

8.2.3 Application Curve

[图 53](#) shows the INA303 device being used in a bidirectional configuration to detect both negative and positive overcurrent events.

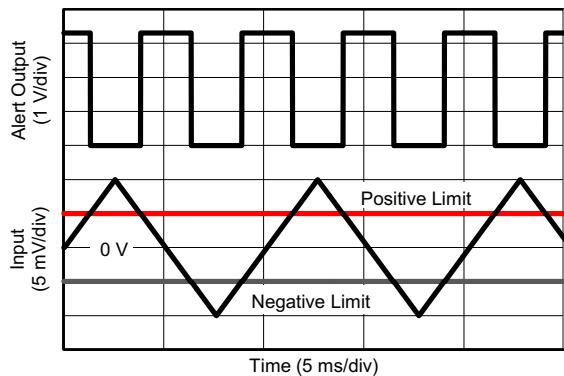


图 53. Bidirectional Application Curve

9 Power Supply Recommendations

The device input circuitry can accurately measure signals on common-mode voltages beyond the power-supply voltage, V_S . For example, the voltage applied to the V_S power-supply pin can be 5 V, whereas the load power-supply voltage being monitored (V_{CM}) can be as high as 36 V. At power-up, for applications where the common-mode voltage (V_{CM}) slew rate is greater than 6 V/ μ s with a final common-mode voltage greater than 20 V, the V_S supply is recommended to be present before V_{CM} . If the use case requires V_{CM} to be present before V_S with V_{CM} under these same slewing conditions, then a 331- Ω resistor must be added between the V_S supply and the V_S pin bypass capacitor.

Power-supply bypass capacitors are required for stability and must be placed as close as possible to the supply and ground pins of the device. A typical value for this supply bypass capacitor is 0.1 μ F. Applications with noisy or high-impedance power supplies can require additional decoupling capacitors to reject power-supply noise.

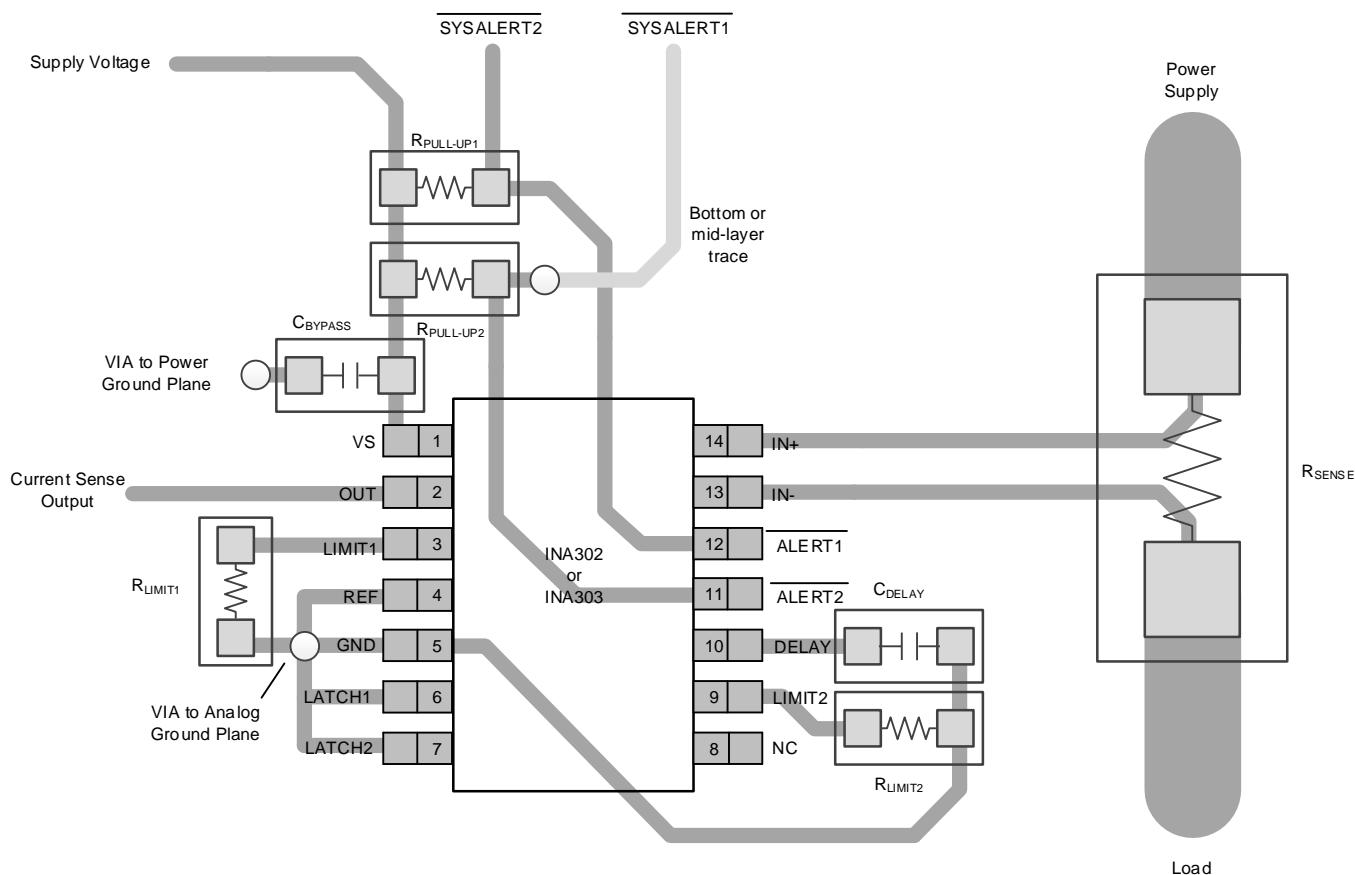
During slow power-up events, current flow through the sense resistor or voltage applied to the REF pin can result in the output voltage momentarily exceeding the voltage at the $LIMIT_x$ pins, resulting in an erroneous indication of an out-of-range event on the $ALERT_x$ output. When powering the device with a slow ramping power rail where an input signal is already present, all alert indications should be disregarded until the supply voltage has reached the final value.

10 Layout

10.1 Layout Guidelines

- Apply connections to the current-sense resistor, R_{SENSE} , on the inside of the resistor pads to avoid additional voltage losses incurred by the high current traces to the resistor. Route the traces from the current-sense resistor symmetrically and side-by-side back to the input of the INA to minimize common-mode errors and noise pickup.
- Place the power-supply bypass capacitor as closely as possible to the supply and ground pins. The recommended value of this bypass capacitor is 0.1 μ F. Additional decoupling capacitance can be added to compensate for noisy or high-impedance power supplies.
- Make the connection of R_{LIMIT} to the ground pin as direct as possible to limit additional capacitance on this node. Routing this connection must be limited to the same plane if possible to avoid vias to internal planes. If the routing can not be made on the same plane and must pass through vias, ensure that a path is routed from R_{LIMIT} back to the ground pin and that R_{LIMIT} is not simply connected directly to a ground plane.
- Routing to the delay capacitor must be short and direct. Keep the routing trace from the $DELAY$ pin to the delay capacitor away from the $ALERT2$ trace (or any other noisy signals) to minimize any coupling effects. If no delay capacitor is used do not have any connection to the $DELAY$ pin. Long trace lengths on the $DELAY$ pin can cause noise to couple to the device, resulting in false trips.
- The open-drain output pins are recommended to be pulled up to the supply voltage rail through a 10-k Ω pullup resistor.

10.2 Layout Example



NOTE: Connect the limit resistors and delay capacitors directly to the GND pin; leave the DELAY pin unconnected or connected to VS through a pullup resistor if no delay is needed.

图 54. Recommended Layout

11 器件和文档支持

11.1 文档支持

11.1.1 相关文档

相关文档请参阅以下部分：

- [《OPAx313 1 MHz、微功耗、低噪声、RRIO、1.8V CMOS 运算放大器精密超值系列》](#)
- [《监测电流以识别多种超出范围的状况》](#)

11.2 相关链接

下面的表格列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，并且可通过快速访问立刻订购。

表 6. 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持与社区
INA302	请单击此处				
INA303	请单击此处				

11.3 接收文档更新通知

如需接收文档更新通知，请访问 www.ti.com.cn 网站上的器件产品文件夹。点击右上角的提醒我 (Alert me) 注册后，即可每周定期收到已更改的产品信息。有关更改的详细信息，请查阅已修订文档中包含的修订历史记录。

11.4 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community **TI's Engineer-to-Engineer (E2E) Community.** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support **TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.5 商标

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

11.6 静电放电警告

 ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

 ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能导致器件与其发布的规格不相符。

11.7 Glossary

[SLYZ022 — TI Glossary.](#)

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页中包括机械封装、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA302A1IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I302A1	Samples
INA302A1IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I302A1	Samples
INA302A2IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I302A2	Samples
INA302A2IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I302A2	Samples
INA302A3IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I302A3	Samples
INA302A3IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I302A3	Samples
INA303A1IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I303A1	Samples
INA303A1IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I303A1	Samples
INA303A2IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I303A2	Samples
INA303A2IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I303A2	Samples
INA303A3IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I303A3	Samples
INA303A3IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	I303A3	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

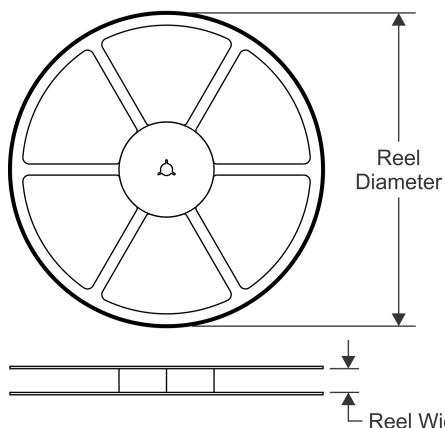
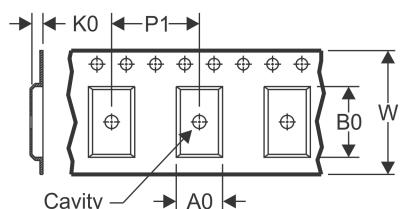
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

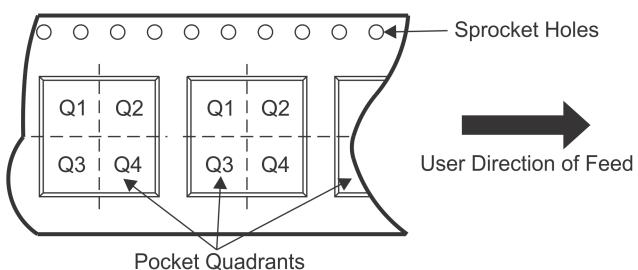
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

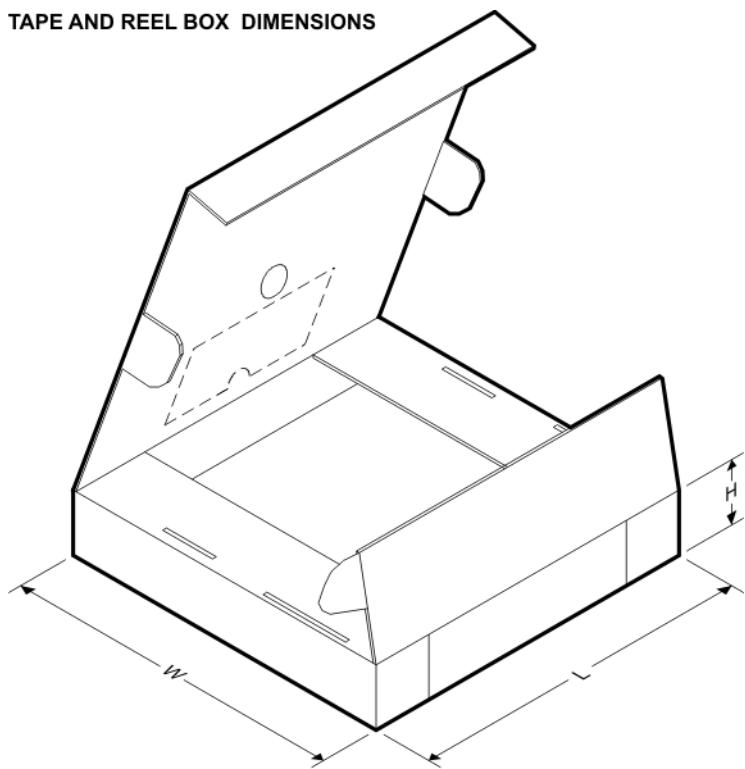
TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA302A1IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
INA302A2IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
INA302A3IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
INA303A1IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
INA303A2IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
INA303A3IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

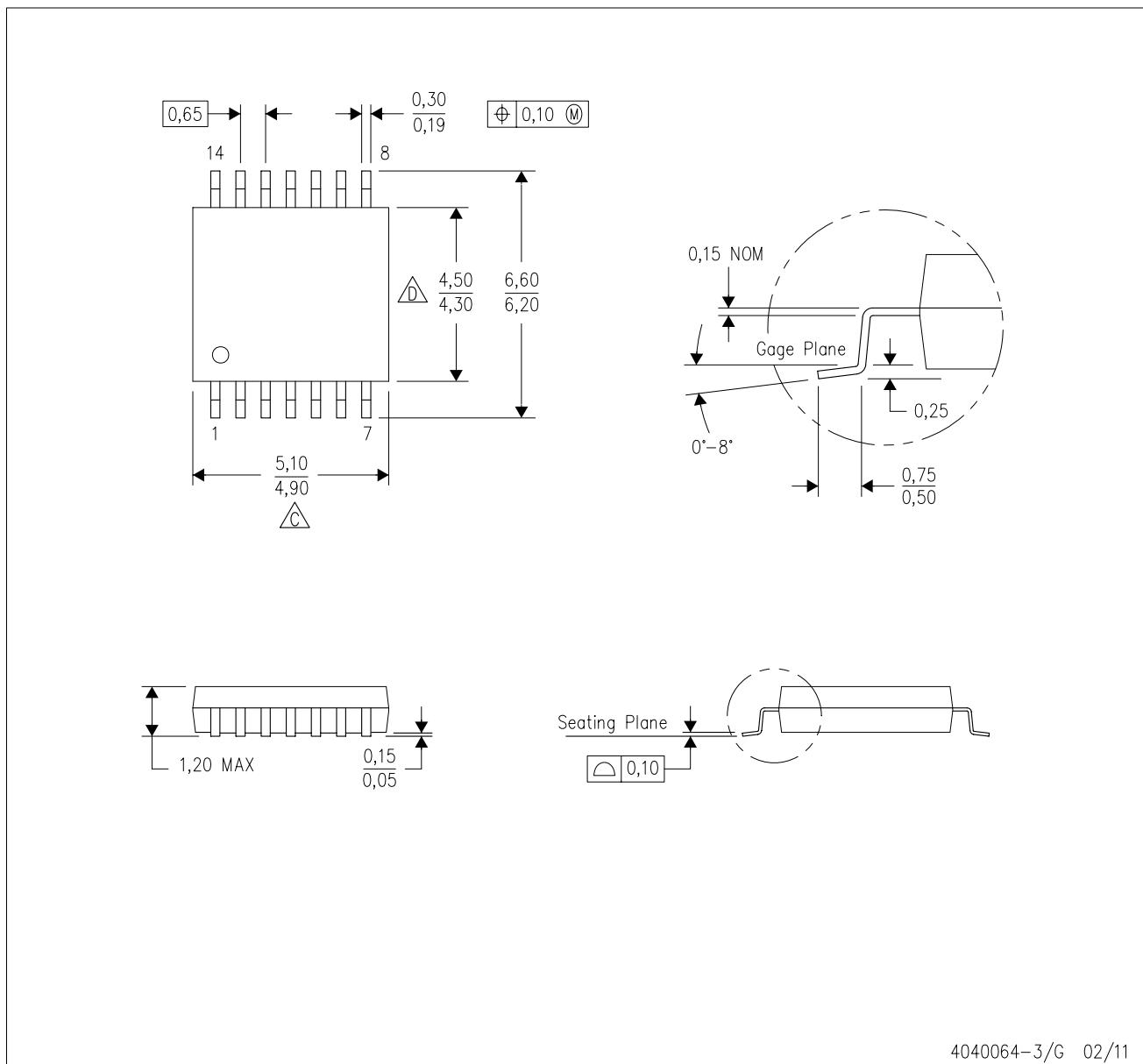
TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA302A1IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
INA302A2IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
INA302A3IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
INA303A1IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
INA303A2IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
INA303A3IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

 C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

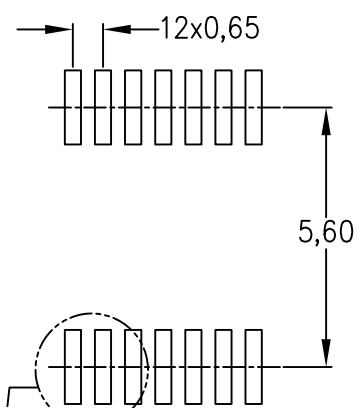
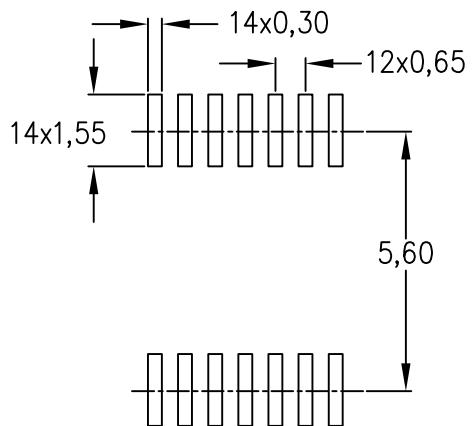
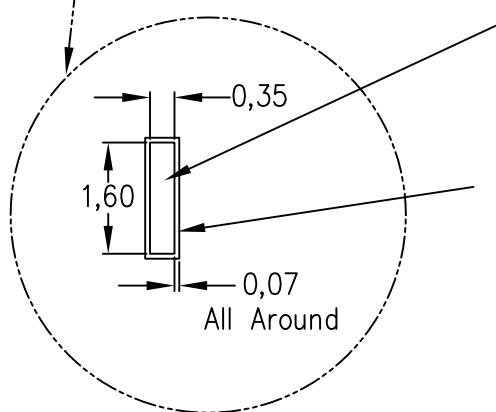
 D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153

4040064-3/G 02/11

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE

Example Board Layout
(Note C)Stencil Openings
(Note D)Example
Non Soldermask Defined PadExample
Pad Geometry
(See Note C)Example
Solder Mask Opening
(See Note E)

4211284-2/G 08/15

NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

重要声明

德州仪器 (TI) 公司有权按照最新发布的 JESD46 对其半导体产品和服务进行纠正、增强、改进和其他修改，并不再按最新发布的 JESD48 提供任何产品和服务。买方在下订单前应获取最新的相关信息，并验证这些信息是否完整且是最新的。

TI 公布的半导体产品销售条款 (<http://www.ti.com/sc/docs/stdterms.htm>) 适用于 TI 已认证和批准上市的已封装集成电路产品的销售。另有其他条款可能适用于其他类型 TI 产品及服务的使用或销售。

复制 TI 数据表上 TI 信息的重要部分时，不得变更该等信息，且必须随附所有相关保证、条件、限制和通知，否则不得复制。TI 对该等复制文件不承担任何责任。第三方信息可能受到其它限制条件的制约。在转售 TI 产品或服务时，如果存在对产品或服务参数的虚假陈述，则会失去相关 TI 产品或服务的明示或暗示保证，且构成不公平的、欺诈性商业行为。TI 对此类虚假陈述不承担任何责任。

买方和在系统中整合 TI 产品的其他开发人员（总称“设计人员”）理解并同意，设计人员在设计应用时应自行实施独立的分析、评价和判断，且应全权负责并确保应用的安全性，及设计人员的应用（包括应用中使用的所有 TI 产品）应符合所有适用的法律法规及其他相关要求。设计人员就自己设计的应用声明，其具备制订和实施下列保障措施所需的一切必要专业知识，能够（1）预见故障的危险后果，（2）监视故障及其后果，以及（3）降低可能导致危险的故障几率并采取适当措施。设计人员同意，在使用或分发包含 TI 产品的任何应用前，将彻底测试该等应用和该等应用中所用 TI 产品的功能。

TI 提供技术、应用或其他设计建议、质量特点、可靠性数据或其他服务或信息，包括但不限于与评估模块有关的参考设计和材料（总称“TI 资源”），旨在帮助设计人员开发整合了 TI 产品的应用，如果设计人员（个人，或如果是代表公司，则为设计人员的公司）以任何方式下载、访问或使用任何特定的 TI 资源，即表示其同意仅为该等目标，按照本通知的条款使用任何特定 TI 资源。

TI 所提供的 TI 资源，并未扩大或以其他方式修改 TI 对 TI 产品的公开适用的质保及质保免责声明；也未导致 TI 承担任何额外的义务或责任。TI 有权对 TI 资源进行纠正、增强、改进和其他修改。除特定 TI 资源的公开文档中明确列出的测试外，TI 未进行任何其他测试。

设计人员只有在开发包含该等 TI 资源所列 TI 产品的应用时，才被授权使用、复制和修改任何相关单项 TI 资源。但并未依据禁止反言原则或其他法理授予您任何 TI 知识产权的任何其他明示或默示的许可，也未授予您 TI 或第三方的任何技术或知识产权的许可，该等产权包括但不限于任何专利权、版权、屏蔽作品权或与使用 TI 产品或服务的任何整合、机器制作、流程相关的其他知识产权。涉及或参考了第三方产品或服务的信息不构成使用此类产品或服务的许可或与其相关的保证或认可。使用 TI 资源可能需要您向第三方获得对该等第三方专利或其他知识产权的许可。

TI 资源系“按原样”提供。TI 兹免除对资源及其使用作出所有其他明确或默认的保证或陈述，包括但不限于对准确性或完整性、产权保证、无屡发故障保证，以及适销性、适合特定用途和不侵犯任何第三方知识产权的任何默认保证。TI 不负责任任何申索，包括但不限于因组合产品所致或与之有关的申索，也不为或对设计人员进行辩护或赔偿，即使该等产品组合已列于 TI 资源或其他地方。对因 TI 资源或其使用引起或与之有关的任何实际的、直接的、特殊的、附带的、间接的、惩罚性的、偶发的、从属或惩戒性损害赔偿，不管 TI 是否获悉可能会产生上述损害赔偿，TI概不负责。

除 TI 已明确指出特定产品已达到特定行业标准（例如 ISO/TS 16949 和 ISO 26262）的要求外，TI 不对未达到任何该等行业标准要求而承担任何责任。

如果 TI 明确宣称产品有助于功能安全或符合行业功能安全标准，则该等产品旨在帮助客户设计和创作自己的符合相关功能安全标准和要求的应用。在应用内使用产品的行为本身不会配有任何安全特性。设计人员必须确保遵守适用于其应用的相关安全要求和标准。设计人员不可将任何 TI 产品用于关乎性命的医疗设备，除非已由各方获得授权的管理人员签署专门的合同对此类应用专门作出规定。关乎性命的医疗设备是指出现故障会导致严重身体伤害或死亡的医疗设备（例如生命保障设备、心脏起搏器、心脏除颤器、人工心脏泵、神经刺激器以及植入设备）。此类设备包括但不限于，美国食品药品监督管理局认定为 III 类设备的设备，以及在美国以外的其他国家或地区认定为同等类别设备的所有医疗设备。

TI 可能明确指定某些产品具备某些特定资格（例如 Q100、军用级或增强型产品）。设计人员同意，其具备一切必要专业知识，可以为自己的应用选择适合的产品，并且正确选择产品的风险由设计人员承担。设计人员单方面负责遵守与该等选择有关的所有法律或监管要求。

设计人员同意向 TI 及其代表全额赔偿因其不遵守本通知条款和条件而引起的任何损害、费用、损失和/或责任。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122
Copyright © 2017 德州仪器半导体技术（上海）有限公司